

=> s Yitzchaik, Shlomo/in

L1 4 YITZCHAIK, SHLOMO/IN

=> d 11 1-4

L1 ANSWER 1 OF 4 USPATFULL  
 AN 2000:27670 USPATFULL  
 TI Self-assembled superlattices and waveguides prepared for use therewith  
 IN Yitzchaik, Shlomo, Evanston, IL, United States  
 Lundquist, Paul M., Bloomington, MN, United States  
 Marks, Tobin J., Evanston, IL, United States  
 PA Northwestern University, Evanston, IL, United States (U.S. corporation)  
 PI US 6033774 20000307  
 AI US 1997-857769 19970515 (8)  
 RLI Continuation of Ser. No. US 1994-355639, filed on 14 Dec 1994, now  
 abandoned  
 DT Utility  
 LN.CNT 854  
 INCL INCLM: 428/333.000  
 INCLS: 252/582.000; 359/328.000; 359/329.000; 359/330.000; 359/332.000;  
 385/122.000; 385/129.000; 385/130.000; 385/131.000; 428/429.000;  
 428/451.000  
 NCL NCLM: 428/333.000  
 NCLS: 252/582.000; 359/328.000; 359/329.000; 359/330.000; 359/332.000;  
 385/122.000; 385/129.000; 385/130.000; 385/131.000; 428/429.000;  
 428/451.000  
 IC [7]  
 ICM: B32B009-04  
 EXF 252/582; 359/328; 359/329; 359/330; 359/332; 385/122; 385/129; 385/130;  
 385/131; 428/333; 428/336; 428/405; 428/429; 428/447; 428/451  
 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L1 ANSWER 2 OF 4 USPATFULL  
 AN 95:108285 USPATFULL  
 TI Photochromic spirooxazine monomers and polysiloxanes  
 IN Krongauz, Valeri, Rehovot, Israel  
 Buchhultz, Frida, Rishon Lezion, Israel  
 Zelichenok, Alexander, Rehovot, Israel  
 Yitzchaik, Shlomo, Evanston, IL, United States  
 PA Yeda Research and Development Co. Ltd. at the Weizmann Institute of  
 Science, Tel Aviv, Israel (non-U.S. corporation)  
 PI US 5473068 19951205  
 AI US 1994-197967 19940217 (8)  
 RLI Division of Ser. No. US 1993-19765, filed on 19 Feb 1993, now patented,  
 Pat. No. US 5322945  
 DT Utility  
 LN.CNT 652  
 INCL INCLM: 544/075.000  
 INCLS: 544/069.000  
 NCL NCLM: 544/071.000  
 NCLS: 544/069.000  
 IC [6]

ICM: C07D498-20  
EXF 544/71; 544/69  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L1 ANSWER 3 OF 4 USPATFULL  
AN 95:65463 USPATFULL  
TI Method and system for producing second order nonlinear optical effects using in-plane poled polymer films  
IN Berkovic, Garry, Rehovot, Israel  
Krongauz, Valeri, Rehovot, Israel  
Yitzchaik, Schlomo, Rehovot, Israel  
Yitzchaik, Shlomo, Holon, Israel  
PA Yeda Research and Development Co., Ltd., Rehovot, Israel (non-U.S. corporation)  
PI US 5434699 19950718  
AI US 1994-214652 19940317 (8)  
RLI Continuation-in-part of Ser. No. US 1993-149395, filed on 9 Nov 1993, now abandoned which is a continuation of Ser. No. US 1991-644371, filed on 23 Jan 1991, now patented, Pat. No. US 5262890  
DT Utility  
LN.CNT 1193  
INCL INCLM: 359/328.000  
NCL NCLM: 359/328.000  
IC [6]  
ICM: G02F001-37  
EXF 359/328

L1 ANSWER 4 OF 4 USPATFULL  
AN 94:53545 USPATFULL  
TI Photochromic spirooxazine monomers and polysiloxanes  
IN Krongauz, Valeri, Rehovot, Israel  
Buchhultz, Frida, Rishon Lezion, Israel  
Zelichenok, Alexander, Rehovot, Israel  
Yitzchaik, Shlomo, Evanston, IL, United States  
PA Yeda Research and Development Co. Ltd., Rehovot, Israel (non-U.S. corporation)  
PI US 5322945 19940621  
AI US 1993-19765 19930219 (8)  
DT Utility  
LN.CNT 691  
INCL INCLM: 544/069.000  
INCLS: 544/071.000; 252/586.000; 351/163.000; 430/345.000; 359/241.000;  
359/642.000  
NCL NCLM: 544/069.000  
NCLS: 252/586.000; 351/163.000; 359/241.000; 359/642.000; 430/345.000;  
544/071.000  
IC [5]  
ICM: C07F007-08  
ICS: C07F007-10; C07F007-18  
EXF 544/69; 544/71; 252/586; 351/163; 350/409; 350/354; 430/345  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s epitaxy

L2 9483 EPITAXY

=> s ?molecular layer?

300982 ?MOLECULAR  
677794 LAYER?  
L3 2933 ?MOLECULAR LAYER?  
(?MOLECULAR (W) LAYER?)

=> s 12 and 13

L4 171 L2 AND L3

=> s 14 and z axis

245850 Z  
759154 AXIS  
22121 Z AXIS  
(Z(W)AXIS)

L5 3 L4 AND Z AXIS

=> s 15 and dianhydride#

6695 DIANHYDRIDE#  
L6 0 L5 AND DIANHYDRIDE#

=> d 15 1-3

L5 ANSWER 1 OF 3 USPATFULL  
AN 1998:116796 USPATFULL

TI Maintaining interatomic distance between an STM probe and a recording  
layer

IN Nose, Hiroyasu, Zama, Japan  
Kawase, Toshimitsu, Atsugi, Japan  
Yamano, Akihiko, Yokohama, Japan

PA Canon Kabushiki Kaisha, Tokyo, Japan (non-U.S. corporation)

PI US 5812516 19980922

AI US 4754654 19950607 (8)

RLI Division of Ser. No. 465908, filed on 6 Jun 1995, now abandoned  
which

is a continuation of Ser. No. 800716, filed on 3 Dec 1991, now  
abandoned which is a continuation of Ser. No. 326677, filed on 21

Mar

1989, now abandoned

PRAI JP 1963-71036 19880325

DT Utility

LN.CNT 942

INCL INCLM: 369/126.000

INCLS: 250/306.000

NCL NCLM: 369/126.000

NCLS: 250/306.000

IC [6]

ICM: G11B009-00

ICS: G06K017-00

EXF 369/126; 369/101; 369/124; 369/112; 250/306; 250/307; 365/151; 365/128

L5 ANSWER 2 OF 3 USPATFULL

AN 97:22626 USPATFULL

TI Method for arranging a polynucleotide on a substrate for point-by-point  
analysis of the bases thereof

IN Fourmentin-Guilbert, Jean E. R., 84, avenue de la Republique, 93160  
Noisy Le Grand, France

PI US 5612181 19970318

AI US 1994-282627 19940729 (8)

RLI Continuation-in-part of Ser. No. US 1992-845918, filed on 4 Mar 1992,  
now abandoned which is a continuation-in-part of Ser. No. US  
1990-541530, filed on 21 Jun 1990, now abandoned

PRAI FR 1989-8284 19890621

DT Utility

LN.CNT 714

INCL INCLM: 435/006.000  
INCL INCLS: 536/025.400  
NCL NCLM: 435/006.000  
NCL NCLS: 536/025.400  
IC [6]  
ICM: C12Q001-68  
ICS: G01N033-24  
EXF 435/6; 536/25.4  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 3 OF 3 USPATFULL  
AN 95:67455 USPATFULL  
TI Ordered mixed crystal semiconductor superlattice device  
IN Nakata, Yoshiaki, Kawasaki, Japan  
Ueda, Osamu, Kawasaki, Japan  
Nakamura, Satoshi, Kawasaki, Japan  
PA Fujitsu Limited, Kawasaki, Japan (non-U.S. corporation)  
PI US 5436468 19950725  
AI US 1994-308217 19940919 (8)  
RLI Continuation of Ser. No. US 1993-31850, filed on 16 Mar 1993, now abandoned  
PRAI JP 1992-60167 19920317  
JP 1992-223793 19920824  
JP 1992-271969 19921009  
DT Utility  
LN.CNT 1518  
INCL INCLM: 257/015.000  
INCLS: 257/014.000; 257/022.000; 257/628.000  
NCL NCLM: 257/015.000  
NCLS: 257/014.000; 257/022.000; 257/628.000  
IC [6]  
ICM: H01L029-04  
ICS: H01L029-161  
EXF 257/15; 257/17; 257/20; 257/21; 257/22; 257/24; 257/194; 257/201; 257/628  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s 14 and dianhydride#

6695 DIANHYDRIDE#  
L7 13 L4 AND DIANHYDRIDE#

=> d 17 1-13

L7 ANSWER 1 OF 13 USPATFULL  
AN 1999:73668 USPATFULL  
TI Optical circuit device, its manufacturing process and a multilayer optical circuit using said optical circuit device  
IN Yoshimura, Tetsuzo, Kawasaki, Japan  
Tatsuura, Satoshi, Kawasaki, Japan  
Sotoyama, Wataru, Kawasaki, Japan  
Yoneda, Yasuhiro, Kawasaki, Japan  
Motoyoshi, Katsusada, Kawasaki, Japan  
Tsukamoto, Koji, Kawasaki, Japan  
Ishitsuka, Takeshi, Kawasaki, Japan  
PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)  
PI US 5917980 19990629  
AI US 1993-28550 19930308 (8)  
PRAI JP 1992-48961 19920306  
JP 1992-52206 19920311  
JP 1992-159350 19920618

JP 1992-179909 19920707  
JP 1992-189554 19920716  
DT Utility  
LN.CNT 1693  
INCL INCLM: 385/129.000  
INCLS: 385/014.000; 385/130.000; 385/131.000; 385/132.000; 385/141.000;  
385/122.000; 385/041.000  
NCL NCLM: 385/129.000  
NCLS: 385/014.000; 385/041.000; 385/122.000; 385/130.000; 385/131.000;  
385/132.000; 385/141.000  
IC [6]  
ICM: G02B006-10  
EXF 385/2; 385/5; 385/7; 385/8; 385/9; 385/11; 385/14; 385/16; 385/24;  
385/27; 385/40; 385/41; 385/43; 385/129; 385/130; 385/131; 385/132;  
385/141; 385/142; 385/143; 385/145; 385/122; 359/1; 359/15; 359/22;  
359/27; 359/34; 359/35  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 2 OF 13 USPATFULL  
AN 1999:27356 USPATFULL  
TI Photosensitive material and process for the preparation thereof  
IN Takimoto, Akio, Neyagawa, Japan  
Wakemoto, Hirofumi, Neyagawa, Japan  
Tanaka, Eiichiro, Kishiwada, Japan  
Watanabe, Masanori, Katano, Japan  
Asayama, Junko, Suita, Japan  
Ogawa, Hisahito, Ikoma-gun, Japan  
Sato, Shigehiro, Osaka, Japan  
Yokotani, Fumiko, Suita, Japan  
PA Matsushita Electric Industrial Co., Ltd., Osaka-fu, Japan (non-U.S.  
corporation)  
PI US 5876891 19990302  
AI US 1995-450909 19950526 (8)  
RLI Division of Ser. No. US 1993-90638, filed on 13 Jul 1993, now patented,  
Pat. No. US 5486442 which is a continuation-in-part of Ser. No. US  
1991-673759, filed on 25 Mar 1991, now abandoned  
PRAI JP 1990-73777 19900323  
JP 1990-73778 19900323  
JP 1990-73779 19900323  
JP 1990-74971 19900325  
JP 1990-335910 19901129  
DT Utility  
LN.CNT 1862  
INCL INCLM: 430/071.000  
INCLS: 430/072.000; 430/078.000; 430/096.000; 430/135.000  
NCL NCLM: 430/071.000  
NCLS: 430/072.000; 430/078.000; 430/096.000; 430/135.000  
IC [6]  
ICM: G03G005-00  
ICS: G03G015-06  
EXF 430/78; 430/96; 430/135; 430/71; 430/72  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 3 OF 13 USPATFULL  
AN 97:68533 USPATFULL  
TI Organic polymer and preparation and use thereof  
IN Takimoto, Akio, Neyagawa, Japan  
Wakemoto, Hirofumi, Neyagawa, Japan  
Tanaka, Eiichiro, Kishiwada, Japan  
Watanabe, Masanori, Katano, Japan  
Asayama, Junko, Suita, Japan  
Ogawa, Hisahito, Ikoma-gun, Japan  
Sato, Shigehiro, Osaka, Japan

PA Yokotani, Fumiko, Suita, Japan  
Matsushita Electric Industrial Co., Ltd., Osaka, Japan (non-U.S.  
corporation)  
PI US 5654367 19970805  
AI US 1995-453061 19950526 (8)  
RLI Division of Ser. No. US 1993-90638, filed on 13 Jul 1993, now patented,  
Pat. No. US 5486442 which is a continuation of Ser. No. US 1991-673759,  
filed on 25 Mar 1991, now abandoned  
PRAI JP 1990-73777 19900323  
JP 1990-73778 19900323  
JP 1990-73779 19900323  
JP 1990-74971 19900325  
JP 1990-335910 19901129  
DT Utility  
LN.CNT 1848  
INCL INCLM: 525/178.000  
INCLS: 525/180.000; 525/181.000; 528/288.000; 528/290.000; 528/295.000;  
528/422.000; 528/425.000  
NCL NCLM: 525/178.000  
NCLS: 525/180.000; 525/181.000; 528/288.000; 528/290.000; 528/295.000;  
528/422.000; 528/425.000  
IC [6]  
ICM: C08F008-30  
ICS: C08L077-00  
EXF 525/178; 525/180; 525/181; 528/272; 528/288; 528/290; 528/295; 528/422;  
528/425  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 4 OF 13 USPATFULL  
AN 97:7990 USPATFULL  
TI Organic polymer and preparation and use thereof  
IN Takimoto, Akio, Neyagawa, Japan  
Wakemoto, Hirofumi, Neyagawa, Japan  
Tanaka, Eiichiro, Kishiwada, Japan  
Watanabe, Masanori, Katano, Japan  
Asayama, Junko, Suita, Japan  
Ogawa, Hisahito, Ikoma-gun, Japan  
Sato, Shigehiro, Osaka, Japan  
Yokotani, Fumiko, Suita, Japan  
PA Matsushita Electric Industrial Co., Ltd., Osaka-fu, Japan (non-U.S.  
corporation)  
PI US 5597889 19970128  
AI US 1995-451727 19950526 (8)  
RLI Division of Ser. No. US 1993-90638, filed on 13 Jul 1993, now patented,  
Pat. No. US 5486442 which is a continuation of Ser. No. US 1991-673759,  
filed on 25 Mar 1991, now abandoned  
PRAI JP 1990-73777 19900323  
JP 1990-73778 19900323  
JP 1990-73779 19900323  
JP 1990-74971 19900325  
JP 1990-335910 19901129  
DT Utility  
LN.CNT 1872  
INCL INCLM: 528/353.000  
INCLS: 528/125.000; 528/126.000; 528/128.000; 528/170.000; 528/172.000;  
528/176.000; 528/183.000; 528/185.000; 528/187.000; 528/188.000;  
528/220.000; 528/229.000; 428/001.000; 428/473.500  
NCL NCLM: 427/058.000  
NCLS: 428/001.260; 428/473.500; 528/125.000; 528/126.000; 528/128.000;  
528/170.000; 528/172.000; 528/176.000; 528/183.000; 528/185.000;  
528/187.000; 528/188.000; 528/220.000; 528/229.000; 528/353.000  
IC [6]  
ICM: C08G069-26

ICS: C09K019-00  
EXF 528/353; 528/125; 528/126; 528/128; 528/170; 528/172; 528/176; 528/183;  
528/185; 528/187; 528/188; 528/220; 528/229; 428/1; 428/473.5  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 5 OF 13 USPATFULL  
AN 96:7632 USPATFULL  
TI Organic polymer and preparation and use in crystal spatial light  
modulator  
IN Takimoto, Akio, Neyagawa, Japan  
Wakemoto, Hirofumi, Neyagawa, Japan  
Tanaka, Eiichiro, Kishiwada, Japan  
Watanabe, Masanori, Katano, Japan  
Asayama, Junko, Suita, Japan  
Ogawa, Hisahito, Ikoma, Japan  
Sato, Shigehiro, Osaka, Japan  
Yokotani, Fumiko, Suita, Japan  
PA Matsushita Electric Industrial Co., Ltd., Osaka, Japan (non-U.S.  
corporation)  
PI US 5486442 19960123  
AI US 1993-90638 19930713 (8)  
RLI Continuation of Ser. No. US 1991-673759, filed on 25 Mar 1991, now  
abandoned  
PRAI JP 1990-73777 19900323  
JP 1990-73778 19900323  
JP 1990-73779 19900323  
JP 1990-74971 19900325  
JP 1990-335910 19901129  
DT Utility  
LN.CNT 1852  
INCL INCLM: 430/078.000  
INCLS: 430/014.000; 430/325.000; 359/067.000; 359/071.000; 359/072.000;  
522/148.000; 522/164.000  
NCL NCLM: 430/078.000  
NCLS: 349/114.000; 349/116.000; 430/325.000; 522/148.000; 522/164.000  
IC [6]  
ICM: G03G005-00  
EXF 430/78; 430/220; 430/325; 359/67; 359/71; 359/72; 522/148; 522/164;  
522/904; 522/905  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 6 OF 13 USPATFULL  
AN 95:76714 USPATFULL  
TI Organic functional optical thin film, fabrication and use thereof  
IN Yoshimura, Tetsuzo, Kawasaki, Japan  
Yano, Ei, Kawasaki, Japan  
Tatsuura, Satoshi, Kawasaki, Japan  
Sotoyama, Wataru, Kawasaki, Japan  
PA Fujitsu Limited, Kawasaki, Japan (non-U.S. corporation)  
PI US 5444811 19950822  
AI US 1992-858074 19920326 (7)  
PRAI JP 1991-132448 19910326  
JP 1991-239559 19910919  
DT Utility  
LN.CNT 2877  
INCL INCLM: 385/141.000  
INCLS: 385/129.000; 385/130.000; 385/131.000; 385/122.000; 385/143.000;  
385/145.000; 427/162.000; 427/163.200; 427/166.000; 427/167.000  
NCL NCLM: 385/141.000  
NCLS: 385/122.000; 385/129.000; 385/130.000; 385/131.000; 385/143.000;  
385/145.000; 427/162.000; 427/163.200; 427/166.000; 427/167.000  
IC [6]  
ICM: G02B006-12

ICS: B05D005-06  
EXF 385/123; 385/122; 385/128; 385/129; 385/130; 385/131; 385/141; 385/143;  
385/145; 385/14; 359/321; 359/326; 359/332; 427/162; 427/164; 427/166;  
427/167; 427/248.1; 427/255.6; 427/269; 427/407.1; 427/410; 427/412.4;  
427/163.2

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 7 OF 13 USPATFULL  
AN 94:91511 USPATFULL  
TI Liquid crystal display devices with organic thin film formed by  
compressing molecules on liquid surface and transferring to substrate  
by horizontal lifting  
IN Imazeki, Shuji, Saitama, Japan  
Tomioka, Yasushi, Saitama, Japan  
Tanaka, Naoki, Saitama, Japan  
Taniguchi, Yoshio, Hino, Japan  
Kawakami, Hideaki, Chiba, Japan  
Kondo, Katsumi, Katsuta, Japan  
Yamasaki, Masami, Saitama, Japan  
PA Hitachi, Ltd., Tokyo, Japan (non-U.S. corporation)  
PI US 5357357 19941018  
AI US 1990-584971 19900919 (7)  
PRAI JP 1989-1241975 19890920  
JP 1989-1241990 19890920  
JP 1989-1246289 19890925  
DT Utility  
LN.CNT 1588  
INCL INCLM: 359/076.000  
INCLS: 359/063.000; 359/075.000; 428/001.000  
NCL NCLM: 428/001.310  
NCLS: 349/095.000; 349/096.000; 349/123.000; 349/132.000  
IC [5]  
ICM: G02F001-1337  
ICS: G02F001-1335; C09K019-00  
EXF 359/75; 359/63; 359/76; 359/87; 428/1  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 8 OF 13 USPATFULL  
AN 93:65916 USPATFULL  
TI Polarizer with patterned diacetylene layer, method for producing the  
same, and liquid crystal display device including such polarizer  
IN Imazeki, Shuji, Saitama, Japan  
Tomioka, Yasushi, Saitama, Japan  
Tanaka, Naoki, Saitama, Japan  
Kanetake, Tatsuo, Saitama, Japan  
Kondo, Seiichi, Saitama, Japan  
Taniguchi, Yoshio, Hino, Japan  
Kondo, Katsumi, Katsuta, Japan  
Kawakami, Hideaki, Chiba, Japan  
PA Hitachi, Ltd., Tokyo, Japan (non-U.S. corporation)  
PI US 5235449 19930810  
AI US 1991-662642 19910301 (7)  
RLI Continuation-in-part of Ser. No. US 1990-584971, filed on 19 Sep 1990  
PRAI JP 1990-49347 19900302  
DT Utility  
LN.CNT 789  
INCL INCLM: 359/063.000  
INCLS: 359/485.000; 359/492.000; 359/500.000  
NCL NCLM: 349/096.000  
NCLS: 359/485.000; 359/492.000; 359/500.000  
IC [5]  
ICM: G02F001-1335

ICS: G02B005-30  
EXF 359/63; 359/64; 359/485; 359/492; 359/500  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 9 OF 13 USPATFULL  
AN 92:85320 USPATFULL  
TI Organic thin film element  
IN Nakayama, Toshio, Fujisawa, Japan  
Gemma, Nobuhiro, Yokohama, Japan  
Miura, Akira, Toride, Japan  
Naito, Katsuyuki, Yokohama, Japan  
Egusa, Syun, Yokohama, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5155566 19921013  
AI US 1991-675964 19910327 (7)  
PRAI JP 1990-75413 19900327  
DT Utility  
LN.CNT 1029  
INCL INCLM: 357/030.000  
INCLS: 357/008.000  
NCL NCLM: 257/040.000  
NCLS: 257/103.000; 257/443.000  
IC [5]  
ICM: H01L027-14  
ICS: H01L031-00  
EXF 357/30R; 357/8  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 10 OF 13 USPATFULL  
AN 91:100776 USPATFULL  
TI Electric-electronic device including polyimide thin film  
IN Uekita, Masakazu, Hyogo, Japan  
Awaji, Hiroshi, Hyogo, Japan  
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S.  
corporation)  
PI US 5072262 19911210  
AI US 1989-418618 19891010 (7)  
RLI Continuation of Ser. No. US 1987-24421, filed on 10 Mar 1987, now  
abandoned  
PRAI JP 1986-54080 19860311  
DT Utility  
LN.CNT 1093  
INCL INCLM: 357/006.000  
INCLS: 357/023.150  
NCL NCLM: 257/410.000  
NCLS: 257/643.000  
IC [5]  
ICM: H01L049-02  
EXF 357/6; 357/8; 357/23.1; 357/23.15  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 11 OF 13 USPATFULL  
AN 91:100248 USPATFULL  
TI Patterned thin film and process for preparing the same  
IN Uekita, Masakazu, Kobe, Japan  
Awaji, Hiroshi, Kobe, Japan  
Murata, Makoto, Kobe, Japan  
Mizunuma, Satoshi, Kobe, Japan  
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S.  
corporation)  
PI US 5071733 19911210  
AI US 1989-459153 19891229 (7)  
RLI Division of Ser. No. US 1988-248683, filed on 23 Sep 1988, now  
patented,

Pat. No. US 4943471 which is a continuation-in-part of Ser. No. US 1987-51350, filed on 19 May 1987, now patented, Pat. No. US 4839219

PRAI JP 1986-116390 19860520  
JP 1986-116391 19860520  
JP 1987-241640 19870925  
JP 1988-106048 19880428

DT Utility  
LN.CNT 918

INCL INCLM: 430/326.000  
INCLS: 430/330.000; 430/270.000

NCL NCLM: 430/326.000  
NCLS: 430/270.100; 430/330.000

IC [5]  
ICM: G03F007-039

EXF 430/326; 430/270; 430/330

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 12 OF 13 USPATFULL  
AN 90:57699 USPATFULL  
TI Patterned thin film and process for preparing the same  
IN Uekita, Masakazu, Kobe, Japan  
Awaji, Hiroshi, Kobe, Japan  
Murata, Makoto, Kobe, Japan  
Mizunuma, Satoshi, Kobe, Japan  
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S.  
corporation)  
PI US 4943471 19900724  
AI US 1988-248683 19880923 (7)  
RLI Continuation-in-part of Ser. No. US 1987-51350, filed on 19 May 1987,  
now patented, Pat. No. US 4839219  
PRAI JP 1986-116390 19860520  
JP 1986-116391 19860520  
JP 1987-241640 19870925  
JP 1988-106048 19880428

DT Utility  
LN.CNT 910

INCL INCLM: 428/220.000  
INCLS: 428/411.100; 428/473.500; 528/183.000; 528/186.000; 528/188.000;  
528/331.000; 528/342.000; 528/348.000; 528/350.000; 528/353.000

NCL NCLM: 428/220.000  
NCLS: 136/263.000; 428/411.100; 428/473.500; 528/183.000; 528/186.000;  
528/188.000; 528/331.000; 528/342.000; 528/348.000; 528/350.000;  
528/353.000

IC [5]  
ICM: B32B027-00  
ICS: B32B027-34

EXF 428/199; 428/220; 428/473.5; 428/411.1; 528/186; 528/188; 528/350;  
528/353; 528/331; 528/342; 528/348; 528/183

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L7 ANSWER 13 OF 13 USPATFULL  
AN 89:47719 USPATFULL  
TI Thin film and device having the same  
IN Uekita, Masakazu, Kobe, Japan  
Awaji, Hiroshi, Kobe, Japan  
PA Kanegafuchi Kagaku Kogyo Kabushiki Kaisha, Osaka, Japan (non-U.S.  
corporation)  
PI US 4839219 19890613  
AI US 1987-51350 19870519 (7)  
PRAI JP 1986-116390 19860520  
JP 1986-116391 19860520

DT Utility  
LN.CNT 1718

INCL    INCLM: 428/220.000  
INCLS: 428/411.100; 428/473.500; 528/183.000; 528/186.000; 528/188.000;  
528/331.000; 528/342.000; 528/348.000; 528/350.000; 528/353.000  
NCL    NCLM: 428/220.000  
NCLS: 136/255.000; 428/411.100; 428/473.500; 528/183.000; 528/186.000;  
528/188.000; 528/331.000; 528/342.000; 528/348.000; 528/350.000;  
528/353.000  
IC      [4]  
ICM: B32B027-00  
ICS: B32B027-34  
EXF     428/473.5; 428/411.1; 428/220; 528/183; 528/186; 528/188; 528/350;  
528/353; 528/331; 528/342; 528/348  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s polymer structure#

278356 POLYMER  
1253435 STRUCTURE#  
L1 4727 POLYMER STRUCTURE#  
(POLYMER (W) STRUCTURE#)

=> s 11 and monomolecular layer#

2655 MONOMOLECULAR  
708881 LAYER#  
1319 MONOMOLECULAR LAYER#  
(MONOMOLECULAR (W) LAYER#)  
L2 21 L1 AND MONOMOLECULAR LAYER#

=> s 12 and z axis

260791 Z  
792308 AXIS  
23922 Z AXIS  
(Z (W) AXIS)  
L3 0 L2 AND Z AXIS

=> s 12 and axial#

388074 AXIAL#  
L4 0 L2 AND AXIAL#

=> s 12 and covalent?

40488 COVALENT?  
L5 8 L2 AND COVALENT?

=> d 15 1-8

L5 ANSWER 1 OF 8 USPATFULL  
AN 96:31696 USPATFULL  
TI Infrared imaging materials  
IN Robillard, Jean J., El Paso, TX, United States  
PA Board of Regents, The University of Texas System, Austin, TX, United  
States (U.S. corporation)  
PI US 5508145 19960416  
AI US 1995-447265 19950522 (8)  
RLI Continuation of Ser. No. US 1992-973026, filed on 6 Nov 1992, now  
patented, Pat. No. US 5434032  
DT Utility  
LN.CNT 688  
INCL INCLM: 430/345.000  
INCLS: 430/495.000; 430/944.000; 430/962.000; 252/586.000  
NCL NCLM: 430/345.000  
NCLS: 252/586.000; 430/495.100; 430/944.000; 430/962.000  
IC [6]  
ICM: G03C001-685

EXF 430/345; 430/346; 430/495; 430/944; 430/962; 252/586; 252/587; 250/330;  
250/316.1

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 2 OF 8 USPATFULL  
AN 95:64802 USPATFULL  
TI Infrared imaging methods and systems  
IN Robillard, Jean J., El Paso, TX, United States  
PA Board of Regents, The University of Texas System, Austin, TX, United  
States (U.S. corporation)  
PI US 5434032 19950718  
AI US 1992-973026 19921106 (7)  
DT Utility  
LN.CNT 741  
INCL INCLM: 430/345.000  
INCLS: 430/347.000; 430/962.000; 250/330.000; 250/316.100; 252/586.000  
NCL NCLM: 430/345.000  
NCLS: 250/316.100; 250/330.000; 252/586.000; 430/347.000; 430/962.000  
IC [6]  
ICM: G03C001-685  
EXF 430/345; 430/347; 430/962; 250/330; 250/316.1; 252/586  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 3 OF 8 USPATFULL  
AN 95:29552 USPATFULL  
TI Biocompatible, low protein adsorption affinity matrix  
IN Braatz, James A., Beltsville, MD, United States  
Heifetz, Aaron H., Columbia, MD, United States  
PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)  
PI US 5403750 19950404  
AI US 1991-682502 19910408 (7)  
RLI Continuation-in-part of Ser. No. US 1991-665498, filed on 6 Mar 1991,  
now patented, Pat. No. US 5169720  
DT Utility  
LN.CNT 1432  
INCL INCLM: 436/531.000  
INCLS: 528/048.000; 528/052.000; 528/053.000; 528/059.000; 528/904.000;  
427/002.130; 427/207.100; 427/221.000; 427/435.000; 210/500.240;  
428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;  
428/425.500; 428/425.600; 604/008.000; 604/019.000; 604/403.000;  
435/174.000; 435/176.000; 435/181.000; 435/182.000; 525/403.000;  
525/418.000; 525/420.000; 525/424.000; 525/454.000; 436/120.000;  
436/129.000; 436/131.000  
NCL NCLM: 436/531.000  
NCLS: 210/500.240; 427/002.130; 427/207.100; 427/221.000; 427/435.000;  
428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;  
428/425.500; 428/425.600; 435/174.000; 435/176.000; 435/181.000;  
435/182.000; 436/120.000; 436/129.000; 436/131.000; 525/403.000;  
525/418.000; 525/420.000; 525/424.000; 525/454.000; 528/048.000;  
528/052.000; 528/053.000; 528/059.000; 528/904.000; 604/008.000;  
604/019.000; 604/403.000  
IC [6]  
ICM: G01N033-545  
EXF 528/48; 528/52; 528/53; 528/59; 528/904; 427/2; 427/207.1; 427/221;  
427/435; 210/500.24; 428/423.1; 428/423.9; 428/424.2; 428/424.6;  
428/425.1; 428/425.5; 428/425.6; 604/8; 604/19; 604/403; 435/174;  
435/176; 435/181; 435/182; 525/403; 525/418; 525/420; 525/424; 525/454;  
436/531; 436/120; 436/128; 436/131  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 4 OF 8 USPATFULL  
AN 91:98251 USPATFULL  
TI Ultraporous thin-film membranes

IN Wrasidlo, Wolfgang J., LaJolla, CA, United States  
PA Memtec America Corporation, Timonium, MD, United States (U.S.  
corporation)  
PI US 5069945 19911203  
AI US 1989-439935 19891121 (7)  
RLI Division of Ser. No. US 1986-920365, filed on 20 Oct 1986, now  
patented,  
Pat. No. US 4814012 which is a division of Ser. No. US 1988-232930,  
filed on 9 Aug 1988, now patented, Pat. No. US 4902424  
DT Utility  
LN.CNT 1230  
INCL INCLM: 427/245.000  
INCLS: 210/490.000; 210/500.370; 210/500.410  
NCL NCLM: 427/245.000  
NCLS: 210/490.000; 210/500.370; 210/500.410  
IC [5]  
ICM: B01D067-00  
EXF 210/490; 210/500.37; 210/500.41; 427/245; 427/246; 264/41; 264/49  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 5 OF 8 USPATFULL  
AN 90:54633 USPATFULL  
TI Chemically modified hydrophilic prepolymers and polymers  
IN Braatz, James A., Beltsville, MD, United States  
Heifetz, Aaron H., Columbia, MD, United States  
Wolfe, Richard A., Ellisville, MO, United States  
Luthra, Narender P., Columbia, MD, United States  
PA W. R. Grace & Co.-Conn, New York, NY, United States (U.S. corporation)  
PI US 4940737 19900710  
AI US 1988-266445 19881102 (7)  
DT Utility  
LN.CNT 1550  
INCL INCLM: 521/103.000  
INCLS: 521/129.000; 521/159.000; 521/905.000; 524/839.000; 524/591.000;  
524/498.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000  
NCL NCLM: 521/103.000  
NCLS: 521/129.000; 521/159.000; 521/905.000; 524/498.000; 524/591.000;  
524/839.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000  
IC [5]  
ICM: C08G018-14  
EXF 521/905; 521/159; 521/129; 521/103; 524/916; 524/839; 524/591; 524/498;  
528/53; 528/904; 528/49; 528/57; 528/59; 527/202  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 6 OF 8 USPATFULL  
AN 90:42602 USPATFULL  
TI Cell growth enhancers and/or antibody production stimulators comprising  
chemically modified hydrophilic polyurea-urethane prepolymers and  
polymers  
IN Heifetz, Aaron H., Columbia, MD, United States  
Wolfe, Richard A., Ellisville, MO, United States  
Braatz, James A., Beltsville, MD, United States  
Luthra, Narender P., Columbia, MD, United States  
PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)  
PI US 4929706 19900529  
AI US 1989-319458 19890303 (7)  
RLI Continuation-in-part of Ser. No. US 1988-266445, filed on 2 Nov 1988  
DT Utility  
LN.CNT 2101  
INCL INCLM: 528/049.000  
INCLS: 528/060.000; 528/066.000  
NCL NCLM: 528/049.000  
NCLS: 528/060.000; 528/066.000

IC [5]  
ICM: C08G018-10  
EXF 528/49; 528/60; 528/66  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 7 OF 8 USPATFULL  
AN 90:13161 USPATFULL  
TI Ultrafiltration thin film membranes  
IN Wrasidlo, Wolfgang J., LaJolla, CA, United States  
PA Memtec North America Corp., Timonium, MD, United States (U.S.  
corporation)  
PI US 4902424 19900220  
AI US 1988-232930 19880809 (7)  
RLI Division of Ser. No. US 1986-920365, filed on 26 Oct 1986, now  
patented,  
Pat. No. US 4814082  
DT Utility  
LN.CNT 1185  
INCL INCLM: 210/500.360  
INCLS: 210/500.370; 210/500.380; 210/500.410  
NCL NCLM: 210/500.360  
NCLS: 210/500.370; 210/500.380; 210/500.410  
IC [4]  
ICM: B01D013-00  
EXF 210/500.41; 210/500.21; 210/500.34; 210/638; 210/654; 210/500.37;  
210/500.36; 210/500.38  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L5 ANSWER 8 OF 8 USPATFULL  
AN 89:20921 USPATFULL  
TI Ultrafiltration thin film membranes  
IN Wrasidlo, Wolfgang J., San Diego, CA, United States  
PA Memtec North America Corporation, Timonium, MD, United States (U.S.  
corporation)  
PI US 4814082 19890321  
AI US 1986-920365 19861020 (6)  
DT Utility  
LN.CNT 1358  
INCL INCLM: 210/490.000  
INCLS: 210/500.370; 210/500.410  
NCL NCLM: 210/490.000  
NCLS: 210/500.370; 210/500.410  
IC [4]  
ICM: B01D013-00  
EXF 210/500.41; 210/500.37; 210/490  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d 12 1-21

L2 ANSWER 1 OF 21 USPATFULL  
AN 1998:131915 USPATFULL  
TI Method for matrix-assisted laser desorption ionization  
IN Koster, Claus, Lilienthal, Germany, Federal Republic of  
Franzen, Jochen, Bremen, Germany, Federal Republic of  
PA Bruker-Franzen Analytik, GmbH, Bremen, Germany, Federal Republic of  
(non-U.S. corporation)  
PI US 5828063 19981027  
AI US 1997-832469 19970402 (8)  
PRAI DE 1996-19617011 19960427  
DT Utility  
LN.CNT 491

INCL INCLM: 250/288.000  
NCL NCLM: 250/288.000  
IC [6]  
ICM: H01J049-10  
EXF 250/288; 250/288A; 250/281; 250/282  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 2 OF 21 USPATFULL  
AN 96:45832 USPATFULL  
TI Multilayer second-order nonlinear optical films of head-to-head, mainchain chromophoric polymers  
IN Wynne, Kenneth J., Fairfax County, VA, United States  
Lindsay, Geoffrey A., Ridgecrest, CA, United States  
Hoover, James M., Ridgecrest, CA, United States  
Stenger-Smith, John, Ridgecrest, CA, United States  
Henry, deceased, Ronald A., late of Ridgecrest, CA, United States by Ann H. Henry, legal representative  
Chafin, Andrew P., Ridgecrest, CA, United States  
PA The United States of America as represented by the Secretary of the Navy, Washington, DC, United States (U.S. government)  
PI US 5520968 19960528  
AI US 1995-435913 19950505 (8)  
DT Utility  
LN.CNT 1173  
INCL INCLM: 428/001.000  
INCLS: 359/326.000; 359/328.000; 428/333.000; 427/434.300  
NCL NCLM: 428/001.310  
NCLS: 359/326.000; 359/328.000; 427/434.300; 428/333.000  
IC [6]  
ICM: G02F001-35  
EXF 359/326; 359/328; 428/1; 428/333; 427/434.3  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 3 OF 21 USPATFULL  
AN 96:31696 USPATFULL  
TI Infrared imaging materials  
IN Robillard, Jean J., El Paso, TX, United States  
PA Board of Regents, The University of Texas System, Austin, TX, United States (U.S. corporation)  
PI US 5508145 19960416  
AI US 1995-447265 19950522 (8)  
RLI Continuation of Ser. No. US 1992-973026, filed on 6 Nov 1992, now patented, Pat. No. US 5434032  
DT Utility  
LN.CNT 688  
INCL INCLM: 430/345.000  
INCLS: 430/495.000; 430/944.000; 430/962.000; 252/586.000  
NCL NCLM: 430/345.000  
NCLS: 252/586.000; 430/495.100; 430/944.000; 430/962.000  
IC [6]  
ICM: G03C001-685  
EXF 430/345; 430/346; 430/495; 430/944; 430/962; 252/586; 252/587; 250/330; 250/316.1  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 4 OF 21 USPATFULL  
AN 95:64802 USPATFULL  
TI Infrared imaging methods and systems  
IN Robillard, Jean J., El Paso, TX, United States  
PA Board of Regents, The University of Texas System, Austin, TX, United States (U.S. corporation)  
PI US 5434032 19950718  
AI US 1992-973026 19921106 (7)

DT Utility  
LN.CNT 741  
INCL INCLM: 430/345.000  
INCLS: 430/347.000; 430/962.000; 250/330.000; 250/316.100; 252/586.000  
NCL NCLM: 430/345.000  
NCLS: 250/316.100; 250/330.000; 252/586.000; 430/347.000; 430/962.000  
IC [6]  
ICM: G03C001-685  
EXF 430/345; 430/347; 430/962; 250/330; 250/316.1; 252/586  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 5 OF 21 USPATFULL  
AN 95:45210 USPATFULL  
TI Solid state ion sensor with polyimide membrane  
IN Brown, Richard B., Ann Arbor, MI, United States  
Cha, Geun-Sig, Ann Arbor, MI, United States  
PA The Board of Regents of The University of Michigan, Ann Arbor, MI,  
United States (U.S. corporation)  
PI US 5417835 19950523  
AI US 1993-137373 19931014 (8)  
RLI Continuation of Ser. No. US 1991-746134, filed on 13 Aug 1991, now  
abandoned And a continuation of Ser. No. US 1989-370897, filed on 23  
Jun 1989, now abandoned  
DT Utility  
LN.CNT 656  
INCL INCLM: 204/403.000  
INCLS: 204/418.000; 257/253.000; 257/414.000; 435/817.000  
NCL NCLM: 204/403.000  
NCLS: 204/418.000; 257/253.000; 257/414.000; 435/817.000  
IC [6]  
ICM: G01N027-26  
EXF 204/418; 204/416; 204/403; 257/253; 257/414; 435/288; 435/291; 435/817  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 6 OF 21 USPATFULL  
AN 95:34267 USPATFULL  
TI Fluoropolymers  
IN Beckerbauer, Richard, Wilmington, DE, United States  
PA E. I. Du Pont de Nemours and Company, Wilmington, DE, United States  
(U.S. corporation)  
PI US 5408021 19950418  
AI US 1993-149593 19931110 (8)  
RLI Division of Ser. No. US 1991-728400, filed on 11 Jul 1991, now  
patented,  
Pat. No. US 5294493, issued on 15 Mar 1994 which is a  
continuation-in-part of Ser. No. US 1990-625586, filed on 7 Dec 1990,  
now abandoned  
DT Utility  
LN.CNT 1101  
INCL INCLM: 526/243.000  
INCLS: 252/299.010  
NCL NCLM: 526/243.000  
NCLS: 252/299.010  
IC [6]  
ICM: C08F126-00  
EXF 526/243  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 7 OF 21 USPATFULL  
AN 95:29552 USPATFULL  
TI Biocompatible, low protein adsorption affinity matrix  
IN Braatz, James A., Beltsville, MD, United States  
Heifetz, Aaron H., Columbia, MD, United States

PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)  
PI US 5403750 19950404  
AI US 1991-682502 19910408 (7)  
RLI Continuation-in-part of Ser. No. US 1991-665498, filed on 6 Mar 1991,  
now patented, Pat. No. US 5169720  
DT Utility  
LN.CNT 1432  
INCL INCLM: 436/531.000  
INCLS: 528/048.000; 528/052.000; 528/053.000; 528/059.000; 528/904.000;  
427/002.130; 427/207.100; 427/221.000; 427/435.000; 210/500.240;  
428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;  
428/425.500; 428/425.600; 604/008.000; 604/019.000; 604/403.000;  
435/174.000; 435/176.000; 435/181.000; 435/182.000; 525/403.000;  
525/418.000; 525/420.000; 525/424.000; 525/454.000; 436/120.000;  
436/129.000; 436/131.000  
NCL NCLM: 436/531.000  
NCLS: 210/500.240; 427/002.130; 427/207.100; 427/221.000; 427/435.000;  
428/423.100; 428/423.900; 428/424.200; 428/424.600; 428/425.100;  
428/425.500; 428/425.600; 435/174.000; 435/176.000; 435/181.000;  
435/182.000; 436/120.000; 436/129.000; 436/131.000; 525/403.000;  
525/418.000; 525/420.000; 525/424.000; 525/454.000; 528/048.000;  
528/052.000; 528/053.000; 528/059.000; 528/904.000; 604/008.000;  
604/019.000; 604/403.000  
IC [6]  
ICM: G01N033-545  
EXF 528/48; 528/52; 528/53; 528/59; 528/904; 427/2; 427/207.1; 427/221;  
427/435; 210/500.24; 428/423.1; 428/423.9; 428/424.2; 428/424.6;  
428/425.1; 428/425.5; 428/425.6; 604/8; 604/19; 604/403; 435/174;  
435/176; 435/181; 435/182; 525/403; 525/418; 525/420; 525/424; 525/454;  
436/531; 436/120; 436/128; 436/131  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 8 OF 21 USPATFULL  
AN 94:22128 USPATFULL  
TI Polymeric films for second order nonlinear optics  
IN Beckerbauer, Richard, Wilmington, DE, United States  
Hsiung, Hui, Wilmington, DE, United States  
Kaku, Mureo, Wilmington, DE, United States  
Rodriguez Parada, Jose M., Wilmington, DE, United States  
Tam, Wilson, Boothwyn, PA, United States  
PA E. I. Du Pont de Nemours and Company, Wilmington, DE, United States  
(U.S. corporation)  
PI US 5294493 19940315  
AI US 1991-728400 19910711 (7)  
RLI Continuation-in-part of Ser. No. US 1990-623586, filed on 7 Dec 1990,  
now abandoned  
DT Utility  
LN.CNT 1182  
INCL INCLM: 428/411.100  
INCLS: 428/421.000; 428/422.000; 428/515.000; 428/520.000; 428/522.000;  
428/913.000  
NCL NCLM: 428/411.100  
NCLS: 428/421.000; 428/422.000; 428/515.000; 428/520.000; 428/522.000;  
428/913.000  
IC [5]  
ICM: B32B009-04  
EXF 428/411.1; 428/421; 428/913; 428/515; 428/520; 428/522; 428/422  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 9 OF 21 USPATFULL  
AN 94:18802 USPATFULL  
TI Electro-optic waveguide deflector using a nonlinear optic film or  
liquid-crystal overlay cell for use in an optical pickup head

IN Revelli, Jr., Joseph F., Rochester, NY, United States  
Penner, Thomas L., Fairport, NY, United States  
Armstrong, Nancy J., Ontario, NY, United States  
Robello, Douglas R., Webster, NY, United States  
Schildkraut, Jay S., Rochester, NY, United States  
PA Eastman Kodak Company, Rochester, NY, United States (U.S. corporation)  
PI US 5291567 19940301  
AI US 1992-916422 19920721 (7)  
DT Utility  
LN.CNT 1317  
INCL INCLM: 385/008.000  
INCLS: 385/014.000; 385/143.000  
NCL NCLM: 385/008.000  
NCLS: 385/014.000; 385/143.000  
IC [5]  
ICM: G02B006-10  
EXF 385/8; 385/14; 385/143  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 10 OF 21 USPATFULL  
AN 93:20643 USPATFULL  
TI Organic nonlinear optical material  
IN Yoshimura, Tetsuzo, Machida, Japan  
PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)  
PI US 5194548 19930316  
AI US 1990-470477 19900126 (7)  
PRAI JP 1989-16352 19890127  
JP 1989-66022 19890320  
JP 1989-66042 19890320  
JP 1989-66048 19890320  
DT Utility  
LN.CNT 1858  
INCL INCLM: 526/285.000  
INCLS: 430/020.000; 526/310.000; 526/311.000; 526/312.000; 526/258.000;  
359/241.000; 359/245.000; 359/280.000  
NCL NCLM: 526/285.000  
NCLS: 359/241.000; 359/245.000; 359/280.000; 430/020.000; 526/258.000;  
526/310.000; 526/311.000; 526/312.000  
IC [5]  
ICM: C08F038-02  
ICS: C08F238-02  
EXF 526/285; 526/310; 526/311; 526/312; 526/258; 430/20  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 11 OF 21 USPATFULL  
AN 91:98251 USPATFULL  
TI Ultraporous thin-film membranes  
IN Wrasidlo, Wolfgang J., LaJolla, CA, United States  
PA Memtec America Corporation, Timonium, MD, United States (U.S.  
corporation)  
PI US 5069945 19911203  
AI US 1989-439935 19891121 (7)  
RLI Division of Ser. No. US 1986-920365, filed on 20 Oct 1986, now  
patented,  
Pat. No. US 4814012 which is a division of Ser. No. US 1988-232930,  
filed on 9 Aug 1988, now patented, Pat. No. US 4902424  
DT Utility  
LN.CNT 1230  
INCL INCLM: 427/245.000  
INCLS: 210/490.000; 210/500.370; 210/500.410  
NCL NCLM: 427/245.000  
NCLS: 210/490.000; 210/500.370; 210/500.410  
IC [5]

ICM: B01D067-00  
EXF 210/490; 210/500.37; 210/500.41; 427/245; 427/246; 264/41; 264/49  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 12 OF 21 USPATFULL  
AN 90:54633 USPATFULL  
TI Chemically modified hydrophilic prepolymers and polymers  
IN Braatz, James A., Beltsville, MD, United States  
Heifetz, Aaron H., Columbia, MD, United States  
Wolfe, Richard A., Ellisville, MO, United States  
Luthra, Narender P., Columbia, MD, United States  
PA W. R. Grace & Co.-Conn, New York, NY, United States (U.S. corporation)  
PI US 4940737 19900710  
AI US 1988-266445 19881102 (7)  
DT Utility  
LN.CNT 1550  
INCL INCLM: 521/103.000  
INCLS: 521/129.000; 521/159.000; 521/905.000; 524/839.000; 524/591.000;  
524/498.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000  
NCL NCLM: 521/103.000  
NCLS: 521/129.000; 521/159.000; 521/905.000; 524/498.000; 524/591.000;  
524/839.000; 528/053.000; 528/057.000; 528/059.000; 528/904.000  
IC [5]  
ICM: C08G018-14  
EXF 521/905; 521/159; 521/129; 521/103; 524/916; 524/839; 524/591; 524/498;  
528/53; 528/904; 528/49; 528/57; 528/59; 527/202  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 13 OF 21 USPATFULL  
AN 90:42602 USPATFULL  
TI Cell growth enhancers and/or antibody production stimulators comprising  
chemically modified hydrophilic polyurea-urethane prepolymers and  
polymers  
IN Heifetz, Aaron H., Columbia, MD, United States  
Wolfe, Richard A., Ellisville, MO, United States  
Braatz, James A., Beltsville, MD, United States  
Luthra, Narender P., Columbia, MD, United States  
PA W. R. Grace & Co.-Conn., New York, NY, United States (U.S. corporation)  
PI US 4929706 19900529  
AI US 1989-319458 19890303 (7)  
RLI Continuation-in-part of Ser. No. US 1988-266445, filed on 2 Nov 1988  
DT Utility  
LN.CNT 2101  
INCL INCLM: 528/049.000  
INCLS: 528/060.000; 528/066.000  
NCL NCLM: 528/049.000  
NCLS: 528/060.000; 528/066.000  
IC [5]  
ICM: C08G018-10  
EXF 528/49; 528/60; 528/66  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 14 OF 21 USPATFULL  
AN 90:13161 USPATFULL  
TI Ultrafiltration thin film membranes  
IN Wrasidlo, Wolfgang J., LaJolla, CA, United States  
PA Memetic North America Corp., Timonium, MD, United States (U.S.  
corporation)  
PI US 4902424 19900220  
AI US 1988-232930 19880809 (7)  
RLI Division of Ser. No. US 1986-920365, filed on 26 Oct 1986, now  
patented,  
Pat. No. US 4814082

DT Utility  
LN.CNT 1185  
INCL INCLM: 210/500.360  
INCLS: 210/500.370; 210/500.380; 210/500.410  
NCL NCLM: 210/500.360  
NCLS: 210/500.370; 210/500.380; 210/500.410  
IC [4]  
ICM: B01D013-00  
EXF 210/500.41; 210/500.21; 210/500.34; 210/638; 210/654; 210/500.37;  
210/500.36; 210/500.38  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 15 OF 21 USPATFULL  
AN 89:20921 USPATFULL  
TI Ultrafiltration thin film membranes  
IN Wrasidlo, Wolfgang J., San Diego, CA, United States  
PA Memtec North America Corporation, Timonium, MD, United States (U.S.  
corporation)  
PI US 4814082 19890321  
AI US 1986-920365 19861020 (6)  
DT Utility  
LN.CNT 1358  
INCL INCLM: 210/490.000  
INCLS: 210/500.370; 210/500.410  
NCL NCLM: 210/490.000  
NCLS: 210/500.370; 210/500.410  
IC [4]  
ICM: B01D013-00  
EXF 210/500.41; 210/500.37; 210/490  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 16 OF 21 USPATFULL  
AN 86:38278 USPATFULL  
TI Material containing microaggregates of metals, inorganic compounds or  
organometallic compounds, more particularly usable in heterogeneous  
catalysis and its production process  
IN Barraud, Andre, Bures-sur-Yvette, France  
Leloup, Jean, Gif sur Yvette, France  
Ruaudel, Annie, Verrieres le Buisson, France  
PA Commissariat a l'Energie Atomique, Paris, France (non-U.S. government)  
PI US 4598056 19860701  
AI US 1984-680354 19841211 (6)  
PRAI FR 1983-19841 19831212  
DT Utility  
LN.CNT 558  
INCL INCLM: 502/004.000  
INCLS: 502/101.000; 502/527.000  
NCL NCLM: 502/004.000  
NCLS: 502/101.000; 502/527.240  
IC [4]  
ICM: B01J035-02 ~  
EXF 502/4; 502/101; 502/527  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 17 OF 21 USPATFULL  
AN 85:4727 USPATFULL  
TI Primary system  
IN Rohowetz, Stanley E., Neenah, WI, United States  
PA American Can Company, Greenwich, CT, United States (U.S. corporation)  
PI US 4495156 19850122  
AI US 1983-455649 19830105 (6)  
DT Utility  
LN.CNT 252

INCL INCLM: 427/384.000  
INCLS: 106/287.190; 252/032.000; 260/429.500; 427/417.000; 427/419.800  
NCL NCLM: 556/014.000  
NCLS: 106/287.190; 427/417.000; 427/419.800; 556/028.000; 556/031.000  
IC [3]  
ICM: B05D001-36  
ICS: B05D007-00; B05D003-02  
EXF 148/6.14R; 148/6.2; 427/388.2; 427/388.4; 427/399; 427/409; 427/407.1;  
427/27; 427/384; 427/417; 427/419.8; 106/287.19; 260/429.5; 252/32  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 18 OF 21 USPATFULL  
AN 84:28589 USPATFULL  
TI Absorbent products, processes and compositions  
IN Korpman, Ralf, Bridgewater, NJ, United States  
PA Johnson & Johnson, New Brunswick, NJ, United States (U.S. corporation)  
PI US 4449977 19840522  
AI US 1981-329642 19811211 (6)  
RLI Continuation-in-part of Ser. No. US 1979-88882, filed on 29 Oct 1979,  
now abandoned  
DT Utility  
LN.CNT 777  
INCL INCLM: 604/366.000  
INCLS: 604/370.000  
NCL NCLM: 604/366.000  
NCLS: 604/370.000  
IC [3]  
ICM: A61F013-16  
EXF 604/327; 604/329; 604/330; 604/331; 604/358; 604/328; 604/366;  
604/346-354; 604/370; 521/65; 521/84; 521/905; 521/916; 260/17R;  
260/17.4BB; 260/17.4ST; 260/17.4UC

L2 ANSWER 19 OF 21 USPATFULL  
AN 82:10703 USPATFULL  
TI Absorbent products  
IN Korpman, Ralf, Bridgewater, NJ, United States  
PA Permacel, New Brunswick, NJ, United States (U.S. corporation)  
PI US 4318408 19820309  
AI US 1979-88881 19791029 (6)  
DT Utility  
LN.CNT 784  
INCL INCLM: 128/287.000  
INCLS: 128/285.000; 128/290.000P; 128/290.000B  
NCL NCLM: 604/368.000  
NCLS: 604/370.000; 604/373.000; 604/904.000  
IC [3]  
ICM: A61F013-16  
EXF 128/284; 128/287; 128/155; 128/156; 128/285; 128/290R; 128/290P;  
128/290B; 128/296  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 20 OF 21 USPATFULL  
AN 80:51295 USPATFULL  
TI Primer system  
IN Rohowetz, Stanley E., Barrington, IL, United States  
PA American Can Company, Greenwich, CT, United States (U.S. corporation)  
PI US 4228221 19801014  
AI US 1979-26906 19790404 (6)  
DT Utility  
LN.CNT 348  
INCL INCLM: 428/469.000  
INCLS: 427/027.000; 427/054.100  
NCL NCLM: 428/469.000

NCLS: 427/470.000; 427/485.000; 427/517.000  
IC [2]  
ICM: B05D003-06  
EXF 427/54; 427/27; 204/158R; 106/287.19; 260/429.5; 428/469  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 21 OF 21 USPATFULL  
AN 78:27961 USPATFULL  
TI Encapsulation of critical chemicals  
IN Leo, Thomas J., Yardley, PA, United States  
Reynolds, Michael J., Morrisville, PA, United States  
PA Wyrough and Loser, Inc., Trenton, NJ, United States (U.S. corporation)  
PI US 4092285 19780530  
AI US 1976-710115 19760730 (5)  
DT Utility  
LN.CNT 994  
INCL INCLM: 260/028.500R  
INCLS: 260/023.000XA; 260/023.700R; 260/023.700A; 260/028.500B;  
260/031.800HR; 260/031.800R; 260/031.800DR; 260/033.600AQ;  
260/033.600PQ; 260/033.600UA; 260/045.750N; 260/045.750V;  
260/045.900QA; 260/045.900D; 260/045.700S; 260/045.700SW;  
260/745.000; 260/757.000; 260/759.000; 427/212.000; 427/220.000;  
427/221.000; 427/222.000; 260/031.800G  
NCL NCLM: 523/334.000  
NCLS: 427/212.000; 427/220.000; 427/221.000; 427/222.000; 523/200.000;  
523/205.000; 524/274.000; 524/297.000; 524/418.000; 524/433.000;  
524/489.000; 524/552.000; 524/574.000; 524/585.000; 524/925.000  
IC [2]  
ICM: C08L091-00  
EXF 260/28.5R; 260/28.5B; 260/31.8HR; 260/31.8PQ; 260/31.8G; 260/31.8R;  
260/31.8DR; 260/33.6AQ; 260/33.6PQ; 260/33.6UA; 260/23XA; 260/23.7R;  
260/45.75N; 260/45.75V; 260/45.9QA; 260/45.9DI; 260/45.7S; 260/45.75W;  
260/745; 260/757; 260/759; 260/23.7A; 427/212; 427/220; 427/221;  
427/222  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s 12 and epitax?

30650 EPITAX?  
L6 1 L2 AND EPITAX?

=> d

L6 ANSWER 1 OF 1 USPATFULL  
AN 93:20643 USPATFULL  
TI Organic nonlinear optical material  
IN Yoshimura, Tetsuzo, Machida, Japan  
PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)  
PI US 5194548 19930316  
AI US 1990-470477 19900126 (7)  
PRAI JP 1989-16352 19890127  
JP 1989-66022 19890320  
JP 1989-66042 19890320  
JP 1989-66048 19890320  
DT Utility  
LN.CNT 1858  
INCL INCLM: 526/285.000  
INCLS: 430/020.000; 526/310.000; 526/311.000; 526/312.000; 526/258.000;  
359/241.000; 359/245.000; 359/280.000  
NCL NCLM: 526/285.000  
NCLS: 359/241.000; 359/245.000; 359/280.000; 430/020.000; 526/258.000;

526/310.000; 526/311.000; 526/312.000

IC [5]

ICM: C08F038-02

ICS: C08F238-02

EXF 526/285; 526/310; 526/311; 526/312; 526/258; 430/20

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> s Burtman, Vladimir/in

L1 0 BURTMAN, VLADIMIR/IN

=> s molecular layer epitaxy

297144 MOLECULAR

625057 LAYER

9672 EPITAXY

L2 32 MOLECULAR LAYER EPITAXY  
(MOLECULAR (W) LAYER (W) EPITAXY)

=> s 12 and z axis

250400 Z

769338 AXIS

22652 Z AXIS

(Z (W) AXIS)

L3 0 L2 AND Z AXIS

=> s 12 and z

250400 Z

L4 4 L2 AND Z

=> s 14 and (tetracarboxylic dianhydride or tetracarboxylic acid dianhydride)

5730 TETRACARBOXYLIC

6450 DIANHYDRIDE

1689 TETRACARBOXYLIC DIANHYDRIDE

(TETRACARBOXYLIC (W) DIANHYDRIDE)

5730 TETRACARBOXYLIC

506851 ACID

6450 DIANHYDRIDE

1375 TETRACARBOXYLIC ACID DIANHYDRIDE

(TETRACARBOXYLIC (W) ACID (W) DIANHYDRIDE)

L5 0 L4 AND (TETRACARBOXYLIC DIANHYDRIDE OR TETRACARBOXYLIC ACID  
DIANHYDRIDE)

=> s 12 and (tetracarboxylic dianhydride or tetracarboxylic acid dianhydride)

5730 TETRACARBOXYLIC

6450 DIANHYDRIDE

1689 TETRACARBOXYLIC DIANHYDRIDE

(TETRACARBOXYLIC (W) DIANHYDRIDE)

5730 TETRACARBOXYLIC

506851 ACID

6450 DIANHYDRIDE

1375 TETRACARBOXYLIC ACID DIANHYDRIDE

(TETRACARBOXYLIC (W) ACID (W) DIANHYDRIDE)

L6 0 L2 AND (TETRACARBOXYLIC DIANHYDRIDE OR TETRACARBOXYLIC ACID  
DIANHYDRIDE)

=> s 12 and bismaleimide#

L7 2466 BISMALEIMIDE#  
0 L2 AND BISMALEIMIDE#

=> s 12 and diamino carbozole#

17618 DIAMINO  
176 CARBOZOLE#  
0 DIAMINO CARBOZOLE#  
(DIAMINO(W)CARBOZOLE#)  
L8 0 L2 AND DIAMINO CARBOZOLE#

=> d 14 1-4

L4 ANSWER 1 OF 4 USPATFULL  
AN 2000:57621 USPATFULL  
TI Molecular wire injection sensors  
IN Keen, Randy E., San Diego, CA, United States  
PA Keensense, Inc., San Diego, CA, United States (U.S. corporation)  
PI US 6060327 20000509  
AI US 1997-856822 19970514 (8)  
DT Utility  
LN.CNT 2968  
INCL INCLM: 436/518.000  
INCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;  
435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;  
436/524.000; 436/525.000; 436/531.000; 436/806.000  
NCL NCLM: 436/518.000  
NCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;  
435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;  
436/524.000; 436/525.000; 436/531.000; 436/806.000  
IC [7]  
ICM: G01N033-543  
EXF 204/400; 204/403; 422/82.01; 422/82.02; 435/6; 435/287.1; 435/287.2;  
436/518; 436/524; 436/525; 436/531; 436/149; 436/150; 436/151; 436/806  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 2 OF 4 USPATFULL  
AN 1998:55176 USPATFULL  
TI Light-emitting diode having narrow luminescence spectrum  
IN Komoto, Satoshi, Tokyo, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5753940 19980519  
AI US 1996-730060 19961015 (8)  
PRAI JP 1995-267373 19951016  
DT Utility  
LN.CNT 748  
INCL INCLM: 257/095.000  
INCLS: 257/098.000; 257/103.000; 257/622.000  
NCL NCLM: 257/095.000  
NCLS: 257/098.000; 257/103.000; 257/622.000  
IC [6]  
ICM: H01L033-00  
EXF 257/89; 257/95; 257/98; 257/103; 257/622; 257/623  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 3 OF 4 USPATFULL  
AN 94:21922 USPATFULL  
TI Process for forming a thin film of silicon  
IN Nishizawa, Junichi, 6-16, Komegafukuro 1-chome, Sandai-shi, Miyagi-ken,  
Japan  
Abe, Hitoshi, 1-3, Otamayashita, Sendai, Japan

PA Suzuki, Soubei, 1-3, Otamayashita, Sendai-shi, Miyagi-ken, Japan  
Research Development Corporation of Japan, Tokyo, Japan (non-U.S.  
corporation)  
Nishizawa, Junichi, Miyagi, Japan (non-U.S. corporation)  
Oki Electric Industry Co., Ltd., Tokyo, Japan (non-U.S. corporation)  
Suzuki, Soubei, Miyagi, Japan (non-U.S. corporation)  
PI US 5294286 19940315  
AI US 1993-3308 19930112 (8)  
RLI Continuation-in-part of Ser. No. US 1990-551631, filed on 10 Jul 1990,  
now abandoned which is a continuation of Ser. No. US 1988-266228, filed  
on 28 Oct 1988, now abandoned which is a continuation of Ser. No. US  
1985-759096, filed on 25 Jul 1985, now abandoned  
PRAI JP 1984-153978 19840726  
DT Utility  
LN.CNT 1043  
INCL INCLM: 156/610.000  
INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.064; 156/DIG.080;  
437/108.000; 437/241.000; 427/255.100  
NCL NCLM: 117/093.000  
NCLS: 117/089.000; 117/102.000; 117/935.000; 438/925.000  
IC [5]  
ICM: C30B025-14  
EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.73; 156/DIG.80; 156/DIG.64;  
422/245; 423/53.1; 423/54.1; 423/86; 423/87; 423/248.1; 423/255.1;  
118/725; 118/726; 219/411; 219/419; 437/108; 437/241  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 4 OF 4 USPATFULL  
AN 92:7155 USPATFULL  
TI Process for preparing a thin film of superconducting compound oxide  
IN Harada, Keizo, Hyogo, Japan  
Fujimori, Naoji, Hyogo, Japan  
Yazu, Shuji, Hyogo, Japan  
Jodai, Tetsuji, Hyogo, Japan  
PA Sumitomo Electric Industries, Ltd., Osaka, Japan (non-U.S. corporation)  
PI US 5084265 19920128  
AI US 1990-525217 19900516 (7)  
RLI Continuation of Ser. No. US 1988-235459, filed on 24 Aug 1988, now  
abandoned  
PRAI JP 1987-209841 19870824  
DT Utility  
LN.CNT 565  
INCL INCLM: 423/592.000  
INCLS: 075/010.110; 075/010.290; 075/010.640  
NCL NCLM: 505/473.000  
NCLS: 075/010.110; 075/010.290; 075/010.640; 423/263.000; 423/593.000;  
505/480.000  
IC [5]  
ICM: C22B004-00  
EXF 075/10.13; 075/10.11; 075/10.29; 075/10.64; 423/592  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d 12 1-32

L2 ANSWER 1 OF 32 USPATFULL  
AN 2000:154526 USPATFULL  
TI Semiconductor memory operating electrically and optically, retaining  
information without power supply  
IN Sakata, Haruhisa, Tokyo, Japan  
Nagao, Yasuyuki, Hasuda, Japan  
Matsushima, Yuichi, Tokorozawa, Japan

PA KDD Corporation, Tokyo, Japan (non-U.S. corporation)  
PI US 6147901 20001114  
AI US 1999-227618 19990108 (9)  
PRAI JP 1998-3471 19980109  
JP 1999-481 19990105  
DT Utility  
LN.CNT 1388  
INCL INCLM: 365/175.000  
INCLS: 365/106.000  
NCL NCLM: 365/175.000  
NCLS: 365/106.000  
IC [7]  
ICM: G11C011-36  
EXF 365/106; 365/112; 365/107; 365/171; 365/173; 365/175; 257/25; 257/85;  
257/113

L2 ANSWER 2 OF 32 USPATFULL  
AN 2000:146720 USPATFULL  
TI Semiconductor device and manufacturing method thereof  
IN Sugiura, Soichi, Mie-ken, Japan  
Watanobe, Hisashi, Mie-ken, Japan  
PA Kabushiki Kaisha Toshiba, Kanagawa-Ken, Japan (non-U.S. corporation)  
PI US 6140675 20001031  
AI US 1999-366357 19990803 (9)  
PRAI JP 1998-223311 19980806  
DT Utility  
LN.CNT 1136  
INCL INCLM: 257/301.000  
INCLS: 257/304.000  
NCL NCLM: 257/301.000  
NCLS: 257/304.000  
IC [7]  
ICM: H01L027-108  
ICS: H01L029-76  
EXF 257/301; 257/304

L2 ANSWER 3 OF 32 USPATFULL  
AN 2000:57621 USPATFULL  
TI Molecular wire injection sensors  
IN Keen, Randy E., San Diego, CA, United States  
PA Keensense, Inc., San Diego, CA, United States (U.S. corporation)  
PI US 6060327 20000509  
AI US 1997-856822 19970514 (8)  
DT Utility  
LN.CNT 2968  
INCL INCLM: 436/518.000  
INCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;  
435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;  
436/524.000; 436/525.000; 436/531.000; 436/806.000  
NCL NCLM: 436/518.000  
NCLS: 204/400.000; 204/403.000; 422/082.010; 422/082.020; 435/006.000;  
435/287.100; 435/287.200; 436/149.000; 436/150.000; 436/151.000;  
436/524.000; 436/525.000; 436/531.000; 436/806.000  
IC [7]  
ICM: G01N033-543  
EXF 204/400; 204/403; 422/82.01; 422/82.02; 435/6; 435/287.1; 435/287.2;  
436/518; 436/524; 436/525; 436/531; 436/149; 436/150; 436/151; 436/806  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 4 OF 32 USPATFULL  
AN 1999:146999 USPATFULL  
TI Thin film capacitor with electrodes having a perovskite structure and a  
metallic conductivity

IN Fukushima, Noburu, Tokyo, Japan  
Kawakubo, Takashi, Kanagawa-ken, Japan  
Shimizu, Tatsuo, Kanagawa-ken, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5986301 19991116  
AI US 1997-858768 19970519 (8)  
RLI Continuation of Ser. No. US 1996-590566, filed on 26 Jan 1996, now abandoned  
PRAI JP 1995-11655 19950127  
JP 1995-235789 19950913  
DT Utility  
LN.CNT 2223  
INCL INCLM: 257/306.000  
INCLS: 257/295.000; 257/310.000  
NCL NCLM: 257/306.000  
NCLS: 257/295.000; 257/310.000  
IC [6]  
ICM: H01L027-108  
ICS: H01L029-76; H01L029-94; H01L031-119  
EXF 257/295; 257/296; 257/306; 257/310; 257/347  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 5 OF 32 USPATFULL  
AN 1999:81766 USPATFULL  
TI Method of producing a bipolar transistor  
IN Aoki, Kenji, Tokyo, Japan  
Akamine, Tadao, Tokyo, Japan  
Kojima, Yoshikazu, Tokyo, Japan  
PA Seiko Instruments Inc., Tokyo, Japan (non-U.S. corporation)  
PI US 5925574 19990720  
AI US 1992-865646 19920410 (7)  
RLI Continuation of Ser. No. US 1990-620624, filed on 3 Dec 1990, now abandoned  
PRAI JP 1989-313724 19891201  
JP 1989-313725 19891201  
DT Utility  
LN.CNT 519  
INCL INCLM: 437/031.000  
INCLS: 437/141.000; 437/160.000; 437/168.000; 148/DIG.017; 148/DIG.034;  
148/DIG.144  
NCL NCLM: 438/309.000  
NCLS: 148/DIG.017; 148/DIG.034; 148/DIG.144; 438/365.000; 438/558.000  
IC [6]  
ICM: H01L021-265  
EXF 437/31; 437/32; 437/141; 437/160; 437/168; 148/DIG.17; 148/DIG.158;  
148/DIG.144; 148/DIG.34  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 6 OF 32 USPATFULL  
AN 1999:79988 USPATFULL  
TI MOS field effect transistor and its manufacturing method  
IN Aoki, Kenji, Tokyo, Japan  
Takada, Ryoji, Tokyo, Japan  
PA Seiko Instruments Inc., Japan (non-U.S. corporation)  
PI US 5923985 19990713  
AI US 1997-782975 19970114 (8)  
RLI Division of Ser. No. US 1995-538980, filed on 5 Oct 1995 which is a continuation of Ser. No. US 1995-441656, filed on 15 May 1995, now abandoned which is a continuation of Ser. No. US 1994-216764, filed on 22 Mar 1994, now abandoned which is a continuation of Ser. No. US 1993-132485, filed on 6 Oct 1993, now abandoned which is a continuation of Ser. No. US 1993-58048, filed on 5 May 1993, now abandoned which is

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Jan 1988, now abandoned  
PRAI JP 1987-321 19870105  
JP 1987-7553 19870116  
JP 1987-11861 19870121  
JP 1987-36618 19870219  
JP 1987-97960 19870421  
JP 1987-119543 19870515  
DT Utility  
LN.CNT 313  
INCL INCLM: 438/301.000  
INCLS: 438/478.000  
NCL NCLM: 438/301.000  
NCLS: 438/478.000  
IC [6]  
ICM: H01L021-336  
ICS: H01L021-20  
EXF 438/142; 438/301; 438/305; 438/478  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 7 OF 32 USPATFULL  
AN 1998:69423 USPATFULL  
TI Electron-beam lithography system and method for drawing nanometer-order  
pattern  
IN Takeno, Shiro, Kanagawa-ken, Japan  
Kanbayashi, Shigeru, Kanagawa-ken, Japan  
Koike, Mitsuo, Kanagawa-ken, Japan  
Doi, Seizo, Tokyo, Japan  
Higashikawa, Iwao, Tokyo, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5767521 19980616  
AI US 1995-528409 19950914 (8)  
PRAI JP 1994-222254 19940916  
JP 1995-232157 19950911  
DT Utility  
LN.CNT 784  
INCL INCLM: 250/492.200  
INCLS: 250/398.000  
NCL NCLM: 250/492.200  
NCLS: 250/398.000  
IC [6]  
ICM: H01J037-04  
EXF 250/492.2; 250/492.22; 250/492.23; 250/398; 250/396R; 250/311; 250/306;  
250/307

L2 ANSWER 8 OF 32 USPATFULL  
AN 1998:55176 USPATFULL  
TI Light-emitting diode having narrow luminescence spectrum  
IN Komoto, Satoshi, Tokyo, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5753940 19980519  
AI US 1996-730060 19961015 (8)  
PRAI JP 1995-267373 19951016  
DT Utility  
LN.CNT 748  
INCL INCLM: 257/095.000  
INCLS: 257/098.000; 257/103.000; 257/622.000  
NCL NCLM: 257/095.000  
NCLS: 257/098.000; 257/103.000; 257/622.000  
IC [6]  
ICM: H01L033-00

EXF 257/89; 257/95; 257/98; 257/103; 257/622; 257/623  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 9 OF 32 USPATFULL  
AN 97:118349 USPATFULL  
TI Insulated-gate transistor having narrow-bandgap-source  
IN Yoshimi, Makoto, Tokyo, Japan  
Inaba, Satoshi, Tokyo, Japan  
Murakoshi, Atsushi, Tokyo, Japan  
Terauchi, Mamoru, Tokyo, Japan  
Shigyo, Naoyuki, Tokyo, Japan  
Matsushita, Yoshiaki, Tokyo, Japan  
Aoki, Masami, Tokyo, Japan  
Hamamoto, Takeshi, Tokyo, Japan  
Ishibashi, Yutaka, Tokyo, Japan  
Ozaki, Tohru, Tokyo, Japan  
Kawaguchiya, Hitomi, Tokyo, Japan  
Matsuzawa, Kazuya, Tokyo, Japan  
Arisumi, Osamu, Tokyo, Japan  
Nishiyama, Akira, Tokyo, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5698869 19971216  
AI US 1995-527515 19950913 (8)  
PRAI JP 1994-218513 19940913  
JP 1994-218593 19940913  
JP 1994-219073 19940913  
JP 1994-305214 19941208  
JP 1994-305241 19941208  
JP 1995-230329 19950907  
DT Utility  
LN.CNT 4279  
INCL INCLM: 257/192.000  
INCLS: 257/066.000; 257/347.000; 257/616.000  
NCL, NCLM: 257/192.000  
NCLS: 257/066.000; 257/347.000; 257/616.000  
IC [6]  
ICM: H01L031-072  
EXF 257/63; 257/65; 257/347; 257/616; 257/631; 257/55; 257/607; 257/192;  
257/66  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 10 OF 32 USPATFULL  
AN 97:111983 USPATFULL  
TI Growth of doped semiconductor monolayers  
IN Nishizawa, Junichi, Miyai-ken, Japan  
Abe, Hitoshi, Miyai-ken, Japan  
Suzuki, Soubei, 1-3, Otamayahshita, Sendai-shi, Miyagi-ken, Japan  
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.  
corporation)  
Nishizawa, Jun-Ichi, Sendai, Japan (non-U.S. individual)  
Oki Electric Company, Tokyo, Japan (non-U.S. corporation)  
Suzuki, Soubei, Sendai, Japan (non-U.S. individual)  
PI US 5693139 19971202  
AI US 1993-77119 19930615 (8)  
RLI Continuation-in-part of Ser. No. US 1991-671995, filed on 18 Mar 1991,  
now abandoned And Ser. No. US 1990-482283, filed on 20 Feb 1990, now  
abandoned which is a continuation of Ser. No. US 1988-234002, filed on  
12 Aug 1988, now abandoned which is a continuation of Ser. No. US  
1985-759087, filed on 25 Jul 1985, now abandoned, said Ser. No. US  
-671995 which is a continuation of Ser. No. US 1989-372156, filed on 27  
Jun 1989, now abandoned which is a continuation of Ser. No. US  
1987-122997, filed on 19 Nov 1987, now abandoned  
PRAI JP 1984-153977 19840726

JP 1984-153980 19840726  
GB 1985-18834 19850725  
DE 1985-3526824 19850726  
FR 1985-11517 19850726  
JP 1986-275425 19861120  
DE 1987-3739450 19871120  
FR 1987-16124 19871120  
GB 1987-27277 19871120  
DT Utility  
LN.CNT 1239  
INCL INCLM: 117/089.000  
INCLS: 117/093.000; 117/102.000; 117/105.000; 117/953.000; 117/954.000;  
117/956.000; 437/102.000; 437/103.000  
NCL NCLM: 117/089.000  
NCLS: 117/093.000; 117/102.000; 117/105.000; 117/953.000; 117/954.000;  
117/956.000  
IC [6]  
ICM: C30B025-14  
EXF 437/102; 437/103; 427/243; 427/255.1; 117/953; 117/954; 117/956;  
117/89;  
117/93; 117/102; 117/105  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 11 OF 32 USPATFULL  
AN 96:82299 USPATFULL  
TI Method and apparatus using organic vapor phase deposition for the  
growth  
of organic thin films with large optical non-linearities  
IN Forrest, Stephen R., Princeton, NJ, United States  
Ban, Vladimir S., Princeton, NJ, United States  
Burrows, Paul E., Princeton, NJ, United States  
Schwartz, Jeffrey, Princeton, NJ, United States  
PA The Trustees of Princeton University, Princeton, NJ, United States  
(U.S.  
corporation)  
PI US 5554220 19960910  
AI US 1995-444252 19950519 (8)  
DT Utility  
LN.CNT 805  
INCL INCLM: 117/088.000  
INCLS: 117/091.000; 117/099.000; 117/102.000; 117/104.000; 117/925.000;  
117/926.000; 117/927.000  
NCL NCLM: 117/088.000  
NCLS: 117/091.000; 117/099.000; 117/102.000; 117/104.000; 117/925.000;  
117/926.000; 117/927.000  
IC [6]  
ICM: C30B029-54  
EXF 117/88; 117/91; 117/99; 117/102; 117/104; 117/925; 117/926; 117/927  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 12 OF 32 USPATFULL  
AN 96:58484 USPATFULL  
TI Semiconductor device comprising a highspeed static induction transistor  
IN Nishizawa, Jun-ichi, 6-16, Komegafukuro 1-chome, Aoka-ku, Sendai-shi,  
Miyagi-ken, 980, Japan  
Kurabayashi, Toru, Sendai, Japan  
PA Research Development Corp. of Japan, Tokyo, Japan (non-U.S.  
corporation)  
Nishizawa, Jun-ichi, Sendai, Japan (non-U.S. individual)  
Zaidan Hojin Handotai Kenkyu Shinokai, Sendai, Japan (non-U.S.  
corporation)  
PI US 5532511 19960702  
AI US 1995-409684 19950323 (8)

RLI Continuation of Ser. No. US 1993-162300, filed on 7 Dec 1993, now abandoned which is a division of Ser. No. US 1992-965722, filed on 23 Oct 1992, now patented, Pat. No. US 5296403  
DT Utility  
LN.CNT 676  
INCL INCLM: 257/627.000  
INCLS: 257/263.000; 257/264.000; 257/268.000; 257/628.000  
NCL NCLM: 257/627.000  
NCLS: 257/263.000; 257/264.000; 257/268.000; 257/628.000  
IC [6]  
ICM: H01L029-04  
ICS: H01L029-80; H01L031-112; H01L031-036  
EXF 257/138; 257/256; 257/263; 257/264; 257/268; 257/272; 257/265; 257/192; 257/183; 257/521; 257/627; 257/628  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 13 OF 32 USPATFULL  
AN 96:53248 USPATFULL  
TI Impurity doping method with adsorbed diffusion source  
IN Nishizawa, Junichi, Miyagi, Japan  
Aoki, Kenji, Tokyo, Japan  
PA Seiko Instruments Inc., Tokyo, Japan (non-U.S. corporation)  
PI US 5527733 19960618  
AI US 1994-198379 19940218 (8)  
RLI Continuation of Ser. No. US 1992-928525, filed on 11 Aug 1992, now abandoned which is a continuation of Ser. No. US 1990-558427, filed on 27 Jul 1990, now abandoned  
DT Utility  
LN.CNT 625  
INCL INCLM: 437/160.000  
INCLS: 437/939.000; 437/950.000  
NCL NCLM: 438/558.000  
IC [6]  
ICM: H01L021-225  
EXF 437/165; 437/166; 437/160; 437/937; 437/939; 437/942; 437/946; 437/950; 148/DIG.17; 148/DIG.34; 148/DIG.38; 148/DIG.144  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 14 OF 32 USPATFULL  
AN 96:6013 USPATFULL  
TI Semiconductor device and method of manufacturing same  
IN Nishizawa, Jun-ichi, Sendai, Japan  
PA Zaidan Hojin Handotai Kenkyu Shinkokai, Miyagi, Japan (non-U.S. corporation)  
PI US 5485017 19960116  
AI US 1994-241447 19940511 (8)  
PRAI JP 1993-147128 19930512  
DT Utility  
LN.CNT 1327  
INCL INCLM: 257/024.000  
INCLS: 257/030.000; 257/038.000; 257/046.000; 257/104.000; 257/136.000; 257/498.000; 257/458.000; 257/523.000; 437/040.000; 437/081.000; 437/105.000; 437/107.000; 437/126.000; 437/228.000  
NCL NCLM: 257/024.000  
NCLS: 257/030.000; 257/038.000; 257/046.000; 257/104.000; 257/136.000; 257/458.000; 257/498.000; 257/523.000; 438/191.000; 438/192.000; 438/268.000  
IC [6]  
ICM: H01L029-06  
ICS: H01L021-265  
EXF 257/24; 257/30; 257/38; 257/46; 257/104; 257/136; 257/458; 257/523; 257/498; 437/40; 437/81; 437/105; 437/107; 437/126; 437/228  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 15 OF 32 USPATFULL  
AN 95:108393 USPATFULL  
TI Vertical insulated gate transistor and method of manufacture  
IN Kakumoto, Munenari, Kawasaki, Japan  
PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)  
PI US 5473176 19951205  
AI US 1994-296913 19940831 (8)  
PRAI JP 1993-217604 19930901  
JP 1994-200470 19940825  
DT Utility  
LN.CNT 766  
INCL INCLM: 257/192.000  
INCLS: 257/263.000; 257/284.000; 257/330.000; 257/333.000; 257/341.000;  
257/622.000; 437/040.000; 437/107.000; 437/133.000; 437/703.000;  
437/228.000; 437/913.000  
NCL NCLM: 257/192.000  
NCLS: 257/263.000; 257/284.000; 257/330.000; 257/333.000; 257/341.000;  
257/622.000; 438/270.000; 438/271.000  
IC [6]  
ICM: H01L029-161  
ICS: H01L021-265  
EXF 257/284; 257/330; 257/333; 257/192; 257/263; 257/341; 257/622; 437/40;  
437/203; 437/107; 437/126; 437/133; 437/228; 437/913

L2 ANSWER 16 OF 32 USPATFULL  
AN 94:70981 USPATFULL  
TI Doping method of barrier region in semiconductor device  
IN Aoki, Kenji, Tokyo, Japan  
Akamine, Tadao, Tokyo, Japan  
Saito, Naoto, Tokyo, Japan  
PA Seiko Instruments Inc., Tokyo, Japan (non-U.S. corporation)  
PI US 5338697 19940816  
AI US 1990-620615 19901203 (7)  
PRAI JP 1989-313719 19891201  
JP 1989-313720 19891201  
JP 1989-313726 19891201  
JP 1989-318553 19891206  
JP 1989-318554 19891206  
DT Utility  
LN.CNT 1090  
INCL INCLM: 437/040.000  
INCLS: 437/041.000; 437/064.000; 437/069.000; 437/160.000; 437/161.000;  
437/950.000; 437/968.000; 148/DIG.037  
NCL NCLM: 438/291.000  
NCLS: 148/DIG.037; 438/298.000; 438/300.000  
IC [5]  
ICM: H01L021-76  
ICS: H01L021-336  
EXF 437/41; 437/44; 437/64; 437/69; 437/160; 437/161; 437/913; 437/950;  
437/968; 437/40; 148/DIG.34; 148/DIG.37; 148/DIG.53; 257/345; 257/398;  
257/399; 257/400; 257/648; 257/652  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 17 OF 32 USPATFULL  
AN 94:70676 USPATFULL  
TI Method of epitaxially growing compound crystal and doping method  
therein  
IN Nishizawa, Jun-ichi, Miyagi, Japan  
Kurabayashi, Toru, Miyagi, Japan  
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.  
corporation)  
PI US 5338389 19940816

AI US 1993-49661 19930421 (8)  
RLI Continuation of Ser. No. US 1992-860253, filed on 31 Mar 1992, now abandoned which is a continuation of Ser. No. US 1991-642965, filed on 18 Jan 1991, now abandoned  
PRAI JP 1990-8399 19900119  
DT Utility  
LN.CNT 719  
INCL INCLM: 117/089.000  
INCLS: 117/953.000; 117/954.000; 117/955.000  
NCL NCLM: 117/089.000  
NCLS: 117/953.000; 117/954.000; 117/955.000  
IC [5]  
ICM: C30B025-02  
EXF 156/601; 156/610; 156/611; 156/612; 156/613; 156/614; 156/DIG.70;  
156/DIG.73; 156/DIG.89  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 18 OF 32 USPATFULL  
AN 94:24239 USPATFULL  
TI Method of manufacturing a static induction field-effect transistor  
IN Nishizawa, Jun-ichi, Sendai, Japan  
Kurabayashi, Toru, Sendai, Japan  
PA Research Development Corp. of Japan, Tokyo, Japan (non-U.S. corporation)  
Jun-ichi Nishizawa, Miyagi, Japan (non-U.S. corporation)  
Zaidan Hojin Handotai Kenkyu Shinkokai, Miyagi, Japan (non-U.S. corporation)  
PI US 5296403 19940322  
AI US 1992-965722 19921023 (7)  
DT Utility  
LN.CNT 622  
INCL INCLM: 437/133.000  
INCLS: 437/909.000; 437/911.000; 437/913.000  
NCL NCLM: 438/198.000  
NCLS: 438/270.000  
IC [5]  
ICM: H01L021-20  
EXF 437/133; 437/107; 437/126; 437/90; 437/909; 437/911; 437/913  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 19 OF 32 USPATFULL  
AN 94:21922 USPATFULL  
TI Process for forming a thin film of silicon  
IN Nishizawa, Junichi, 6-16, Komegafukuro 1-chome, Sandai-shi, Miyagi-ken, Japan  
Abe, Hitoshi, 1-3, Otamayashita, Sendai, Japan  
Suzuki, Soubei, 1-3, Otamayashita, Sendai-shi, Miyagi-ken, Japan  
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S. corporation)  
Nishizawa, Junichi, Miyagi, Japan (non-U.S. corporation)  
Oki Electric Industry Co., Ltd., Tokyo, Japan (non-U.S. corporation)  
Suzuki, Soubei, Miyagi, Japan (non-U.S. corporation)  
PI US 5294286 19940315  
AI US 1993-3308 19930112 (8)  
RLI Continuation-in-part of Ser. No. US 1990-551631, filed on 10 Jul 1990, now abandoned which is a continuation of Ser. No. US 1988-266228, filed on 28 Oct 1988, now abandoned which is a continuation of Ser. No. US 1985-759096, filed on 25 Jul 1985, now abandoned  
PRAI JP 1984-153978 19840726  
DT Utility  
LN.CNT 1043  
INCL INCLM: 156/610.000  
INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.064; 156/DIG.080;

437/108.000; 437/241.000; 427/255.100  
NCL NCLM: 117/093.000  
NCLS: 117/089.000; 117/102.000; 117/935.000; 438/925.000  
IC [5]  
ICM: C30B025-14  
EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.73; 156/DIG.80; 156/DIG.64;  
422/245; 423/53.1; 423/54.1; 423/86; 423/87; 423/248.1; 423/255.1;  
118/725; 118/726; 219/411; 219/419; 437/108; 437/241  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 20 OF 32 USPATFULL  
AN -93:86995 USPATFULL  
TI Method of epitaxially growing semiconductor crystal using light as a  
detector  
IN Nishizawa, Jun-ichi, 6-16, Komegafukuro 1-chome, Aoba-ku, Sendai-shi,  
Miyagi-ken, Japan  
Kurabayashi, Toru, Sendai, Japan  
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.  
corporation)  
Nishizawa, Jun-ichi, Sendai, Japan (non-U.S. individual)  
Hojin, Zaidan, all of, Japan (non-U.S. individual)  
Shinkoka, Handotai Kenkyu, all of, Japan (non-U.S. individual)  
PI US 5254207 19931019  
AI US 1992-983331 19921130 (7)  
PRAI JP 1991-342448 19911130  
DT Utility  
LN.CNT 522  
INCL INCLM: 156/601.000  
INCLS: 156/612.000; 356/382.000; 356/318.000  
NCL NCLM: 117/086.000  
NCLS: 117/954.000; 356/318.000; 356/382.000  
IC [5]  
ICM: C30B023-02  
EXF 156/612; 156/601; 356/317; 356/318; 356/319; 356/330; 356/346; 356/382  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 21 OF 32 USPATFULL  
AN 93:78385 USPATFULL  
TI Method for growing single crystal thin films of element semiconductor  
IN Nishizawa, Junichi, 6-16, Komegafukuro 1-chome, Sendai-shi, Miyagi,  
Japan  
Aoki, Kenji, Matsudo, Japan  
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.  
corporation)  
Nishizawa, Junichi, Tokyo, Japan (non-U.S. individual)  
Seiko Instruments\*, Sendai, Japan (non-U.S. corporation)  
PI US 5246536 19930921  
AI US 1989-321623 19890310 (7)  
RLI Division of Ser. No. US 1987-93505, filed on 4 Sep 1987, now patented,  
Pat. No. US 4831831  
PRAI JP 1986-209575 19860908  
DT Utility  
LN.CNT 378  
INCL INCLM: 156/610.000  
INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.064; 437/241.000  
NCL NCLM: 117/102.000  
NCLS: 117/935.000  
IC [5]  
ICM: C30B025-14  
EXF 156/616; 156/611; 156/613; 156/614; 156/DIG.64; 427/255.1; 437/241  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 22 OF 32 USPATFULL

AN 93:20643 USPATFULL  
TI Organic nonlinear optical material  
IN Yoshimura, Tetsuzo, Machida, Japan  
PA Fujitsu Limited, Kanagawa, Japan (non-U.S. corporation)  
PI US 5194548 19930316  
AI US 1990-470477 19900126 (7)  
PRAI JP 1989-16352 19890127  
JP 1989-66022 19890320  
JP 1989-66042 19890320  
JP 1989-66048 19890320  
DT Utility  
LN.CNT 1858  
INCL INCLM: 526/285.000  
INCLS: 430/020.000; 526/310.000; 526/311.000; 526/312.000; 526/258.000;  
359/241.000; 359/245.000; 359/280.000  
NCL NCLM: 526/285.000  
NCLS: 359/241.000; 359/245.000; 359/280.000; 430/020.000; 526/258.000;  
526/310.000; 526/311.000; 526/312.000  
IC [5]  
ICM: C08F038-02  
ICS: C08F238-02  
EXF 526/285; 526/310; 526/311; 526/312; 526/258; 430/20  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 23 OF 32 USPATFULL  
AN 92:51014 USPATFULL  
TI Method of producing field effect transistor  
IN Saito, Naoto, Tokyo, Japan  
Aoki, Kenji, Tokyo, Japan  
Akamine, Tadao, Tokyo, Japan  
Kojima, Yoshikazu, Tokyo, Japan  
Takahashi, Kunihiro, Tokyo, Japan  
Kinbara, Masahiko, Tokyo, Japan  
PA Seiko Instruments, Inc., Tokyo, Japan (non-U.S. corporation)  
PI US 5124272 19920623  
AI US 1990-565960 19900813 (7)  
PRAI JP 1989-209287 19890811  
JP 1989-209288 19890811  
JP 1989-209289 19890811  
JP 1989-209291 19890811  
JP 1989-213192 19890818  
JP 1989-231276 19890906  
JP 1989-231277 19890906  
JP 1989-231279 19890906  
JP 1989-231280 19890906  
JP 1989-318557 19891206  
JP 1989-318558 19891206  
DT Utility  
LN.CNT 1369  
INCL INCLM: 437/041.000  
INCLS: 437/044.000; 437/045.000; 437/192.000; 437/946.000  
NCL NCLM: 438/297.000  
NCLS: 438/300.000; 438/301.000; 438/307.000  
IC [5]  
ICM: H01L021-265  
EXF 437/41; 437/40; 437/44; 437/192; 437/45; 437/913; 437/946

L2 ANSWER 24 OF 32 USPATFULL  
AN 92:41010 USPATFULL  
TI Step-cut insulated gate static induction transistors and method of  
manufacturing the same  
IN Nishizawa, Junichi, Sendai, Japan  
Takeda, Nobuo, Sendai, Japan

PA Suzuki, Sohbe, Sendai, Japan  
Research Development Corporation of Japan, Tokyo, Japan (non-U.S. corporation)  
PI US 5115287 19920519  
AI US 1991-752934 19910830 (7)  
RLI Continuation of Ser. No. US 1990-527677, filed on 23 May 1990, now abandoned which is a continuation of Ser. No. US 1987-122720, filed on 18 Nov 1987, now abandoned  
PRAI JP 1986-273934 19861119  
JP 1986-273935 19861119  
JP 1986-276754 19861121  
JP 1986-276755 19861121  
DT Utility  
LN.CNT 897  
INCL INCLM: 357/023.400  
INCLS: 357/023.120; 357/041.000; 357/055.000  
NCL NCLM: 257/334.000  
NCLS: 257/332.000  
IC [5]  
ICM: H01L029-10  
ICS: H01L029-78; H01L029-06  
EXF 357/23.4; 357/55; 357/23.12; 357/41

L2 ANSWER 25 OF 32 USPATFULL  
AN 92:7155 USPATFULL  
TI Process for preparing a thin film of superconducting compound oxide  
IN Harada, Keizo, Hyogo, Japan  
Fujimori, Naoji, Hyogo, Japan  
Yazu, Shuji, Hyogo, Japan  
Jodai, Tetsuji, Hyogo, Japan  
PA Sumitomo Electric Industries, Ltd., Osaka, Japan (non-U.S. corporation)  
PI US 5084265 19920128  
AI US 1990-525217 19900516 (7)  
RLI Continuation of Ser. No. US 1988-235459, filed on 24 Aug 1988, now abandoned  
PRAI JP 1987-209841 19870824  
DT Utility  
LN.CNT 565  
INCL INCLM: 423/592.000  
INCLS: 075/010.110; 075/010.290; 075/010.640  
NCL NCLM: 505/473.000  
NCLS: 075/010.110; 075/010.290; 075/010.640; 423/263.000; 423/593.000;  
505/480.000  
IC [5]  
ICM: C22B004-00  
EXF 075/10.13; 075/10.11; 075/10.29; 075/10.64; 423/592  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 26 OF 32 USPATFULL  
AN 91:82067 USPATFULL  
TI Controlled high rate deposition of metal oxide films  
IN Bunshah, Rointan F., Playa del Rey, CA, United States  
Deshpandey, Chandra V., Los Angeles, CA, United States  
Doerr, Hans J., Westlake Village, CA, United States  
Yoon, Jong S., Northridge, CA, United States  
PA The Regents of the University of California, Oakland, CA, United States (U.S. corporation)  
PI US 5055319 19911008  
AI US 1990-503298 19900402 (7)  
DT Utility  
LN.CNT 604  
INCL INCLM: 427/038.000  
INCLS: 427/042.000; 427/050.000; 427/255.000; 427/255.300; 427/294.000;

427/295.000; 427/314.000; 427/319.000  
NCL NCLM: 427/567.000  
NCLS: 427/294.000; 427/295.000; 427/314.000; 427/319.000; 427/576.000;  
427/587.000

IC [5]  
ICM: B05D003-06

EXF 427/35; 427/42; 427/38; 427/50; 427/255.3; 427/255; 427/294; 427/295;  
427/314; 427/319

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 27 OF 32 USPATFULL

AN 91:61117 USPATFULL

TI Insulated gate semiconductor device using compound semiconductor at the  
channel

IN Shimbo, Masafumi, Tokyo, Japan

PA Seiko Instruments Inc., Japan (non-U.S. corporation)

PI US 5036374 19910730

AI US 1988-180359 19880411 (7)

PRAI JP 1987-87370 19870409

DT Utility

LN.CNT 315

INCL INCLM: 357/023.200

INCLS: 357/023.150; 357/016.000; 437/132.000

NCL NCLM: 257/192.000

NCLS: 257/289.000; 257/410.000; 438/285.000

IC [5]

ICM: H01L029-20

ICS: H01L029-78; H01L029-161; H01L021-20

EXF 357/23.2; 357/23.15; 357/16; 437/132

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 28 OF 32 USPATFULL

AN 90:17942 USPATFULL

TI X-ray image intensifier and method of manufacturing the same

IN Homma, Katsuhisa, Kawasaki, Japan

Kimura, Sakae, Tokyo, Japan

Nikaido, Masaru, Miura, Japan

Ouchi, Yoshiaki, Yokohama, Japan

Obata, Yoshiharu, Ootawara, Japan

Uemura, Yoshikazu, Ootawara, Japan

Sato, Syozo, Sagamihara, Japan

PA Kabushiki Kaisha Toshiba, Kawasaki, Japan (non-U.S. corporation)

PI US 4906893 19900306

AI US 1988-286865 19881220 (7)

PRAI JP 1987-327512 19871225

JP 1988-251932 19881007

DT Utility

LN.CNT 629

INCL INCLM: 313/525.000

INCLS: 313/467.000; 250/486.100; 427/064.000; 427/068.000

NCL NCLM: 313/525.000

NCLS: 250/486.100; 313/467.000; 427/064.000; 427/068.000; 976/DIG.439

IC [4]

ICM: H01J029-20

ICS: B05D005-12

EXF 313/525; 313/467; 313/469; 427/64; 427/68; 427/69; 250/486.1;

252/301.6S

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 29 OF 32 USPATFULL

AN 89:71670 USPATFULL

TI Method of growing group III-V compound semiconductor epitaxial layer

IN Mochizuki, Kouji, Isehara, Japan

Ozeki, Masashi, Yokohama, Japan  
Ohtsuka, Nobuyuki, Atsugi, Japan  
PA Fujitsu Limited, Kawasaki, Japan (non-U.S. corporation)  
PI US 4861417 19890829  
AI US 1988-172671 19880324 (7)  
PRAI JP 1987-71747 19870327  
DT Utility  
LN.CNT 666  
INCL INCLM: 156/610.000  
INCLS: 156/611.000; 156/613.000; 156/614.000; 156/DIG.061; 156/DIG.081;  
156/DIG.094; 156/DIG.103  
NCL NCLM: 117/089.000  
NCLS: 117/101.000; 117/104.000; 117/105.000; 117/902.000; 117/939.000;  
117/954.000  
IC [4]  
ICM: C30B025-14  
EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.61; 156/DIG.81; 156/DIG.94;  
156/DIG.103; 437/236  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 30 OF 32 USPATFULL  
AN 89:69723 USPATFULL  
TI Method for epitaxial growth of compound semiconductor using MOCVD with  
molecular layer epitaxy  
IN Matsumoto, Fumio, Miyagi, Japan  
PA Research Development Corporation of Japan, Junichi Nishizawa and Oki  
Electric Industry Co., Ltd., Japan (non-U.S. corporation)  
PI US 4859625 19890822  
AI US 1987-123497 19871120 (7)  
PRAI JP 1986-277829 19861122  
DT Utility  
LN.CNT 878  
INCL INCLM: 437/081.000  
INCLS: 148/DIG.025; 148/DIG.041; 148/DIG.048; 148/DIG.057; 148/DIG.072;  
148/DIG.110; 148/DIG.094; 156/613.000; 437/019.000; 437/111.000;  
437/133.000; 437/173.000; 437/936.000; 437/942.000; 437/963.000;  
427/053.100  
NCL NCLM: 117/093.000  
NCLS: 117/089.000; 117/092.000; 117/103.000; 117/953.000; 117/954.000;  
117/955.000; 117/956.000; 148/DIG.025; 148/DIG.041; 148/DIG.048;  
148/DIG.057; 148/DIG.072; 148/DIG.094; 148/DIG.110; 427/584.000;  
427/586.000; 438/935.000  
IC [4]  
ICM: H01L021-205  
EXF 148/DIG.6; 148/21; 148/25; 148/41; 148/48; 148/56; 148/65; 148/71;  
148/72; 148/94; 148/110; 148/160; 148/169; 148/57; 156/610-614;  
427/53.1; 427/54.1; 437/19; 437/81; 437/107; 437/108; 437/110; 437/111;  
437/133; 437/173; 437/936; 437/942; 437/949; 437/963  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 31 OF 32 USPATFULL  
AN 89:42995 USPATFULL  
TI Method for growing single crystal thin films of element semiconductor  
IN Nishizawa, Junichi, Sendai, Japan  
Aoki, Kenji, Matsudo, Japan  
PA Research Development Corporation of Japan, Tokyo, Japan (non-U.S.  
corporation)  
Junichi Nishizawa, Sendai, Japan (non-U.S. corporation)  
Seiko Instruments, Inc., Tokyo, Japan (non-U.S. corporation)  
PI US 4834831 19890530  
AI US 1987-93505 19870904 (7)  
PRAI JP 1986-209575 19860908  
DT Utility

LN.CNT 350  
INCL INCLM: 156/611.000  
INCLS: 156/610.000; 156/613.000; 156/614.000; 156/DIG.064; 156/DIG.102;  
156/DIG.103  
NCL NCLM: 117/093.000  
NCLS: 117/935.000  
IC [4]  
ICM: C30B025-10  
ICS: C30B025-14  
EXF 156/610; 156/611; 156/613; 156/614; 156/DIG.64; 156/DIG.102;  
156/DIG.103  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L2 ANSWER 32 OF 32 USPATFULL  
AN 88:55290 USPATFULL  
TI Preparation process of compound semiconductor  
IN Kobayashi, Naoki, Iruma, Japan  
Makimoto, Toshiki, Tokorozawa, Japan  
Horikoshi, Yoshiji, Akishima, Japan  
PA Nippon Telegraph & Telephone Corporation, Tokyo, Japan (non-U.S.  
corporation)  
PI US 4767494 19880830  
AI US 1986-909287 19860919 (6)  
PRAI JP 1986-156260 19860704  
JP 1986-176611 19860729  
DT Utility  
LN.CNT 2116  
INCL INCLM: 156/606.000  
INCLS: 156/613.000; 437/110.000  
NCL NCLM: 117/093.000  
NCLS: 117/939.000; 117/953.000; 117/954.000; 117/955.000  
IC [4]  
ICM: C30B025-02  
EXF 156/606; 156/610; 156/612; 156/613; 156/DIG.70; 156/DIG.89;  
156/DIG.113;  
148/DIG.72; 148/DIG.160; 427/51; 427/86; 437/110  
CAS INDEXING IS AVAILABLE FOR THIS PATENT.